ADVANTECH

DRAM Memory Module

Portfolio Introduction

PAPS Product Management
Q3 / 2013

PART I.

ADVANTECH QUALIFIED DIMM

(AQD)

ADVANTECH QUALIFIED DIMM

Built to Last ---

The toughest memory module for rigorous applications

QUALITY

RELIABILITY

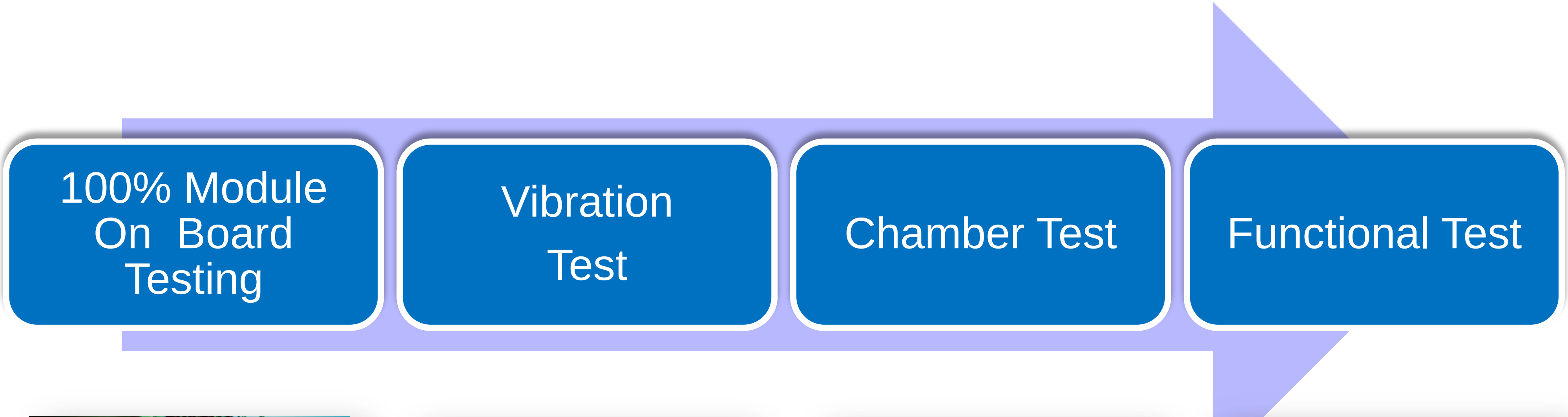
COMPATIBILITY

LONGEVITY

LIFE-TIME WARRANTY

Quality Assurance Program

- Carefully Selected Premium Materials
- ISO-9000 Manufacturing Process
- Industrial Testing Standard



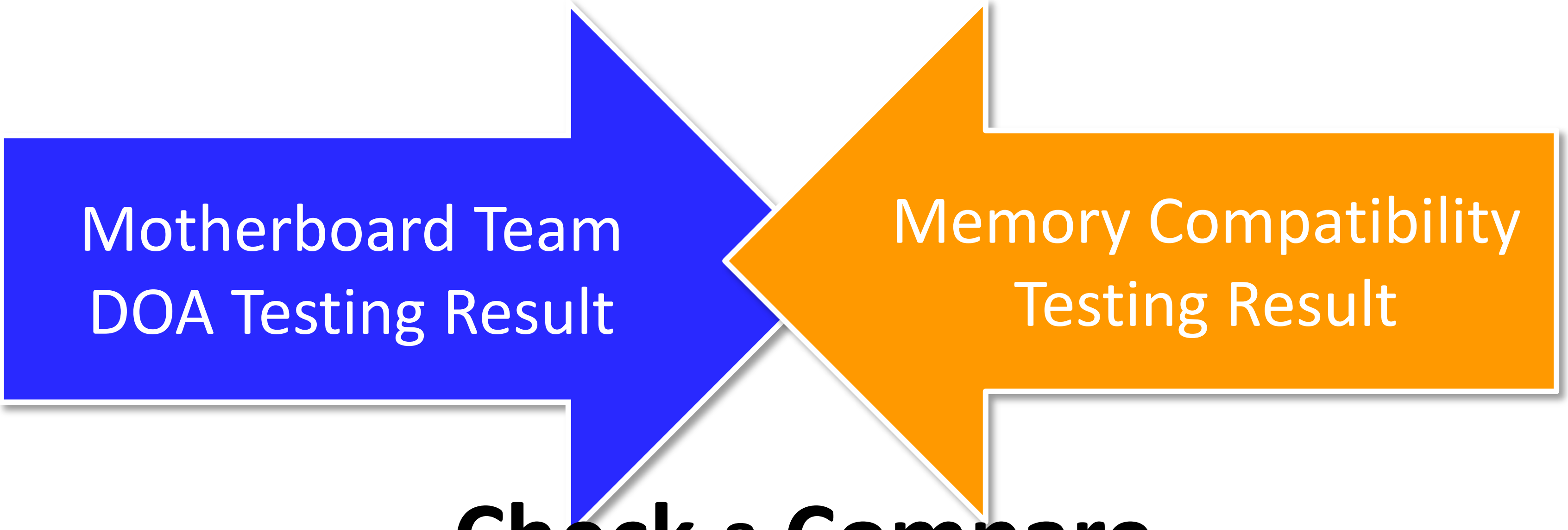
100% Module On Board Testing

Vibration Test

Chamber Test

Functional Test

Quality Assurance | Rigorous Reliability Tests | **Cross-Checked Compatibility** | Longevity | Life-Time Warranty

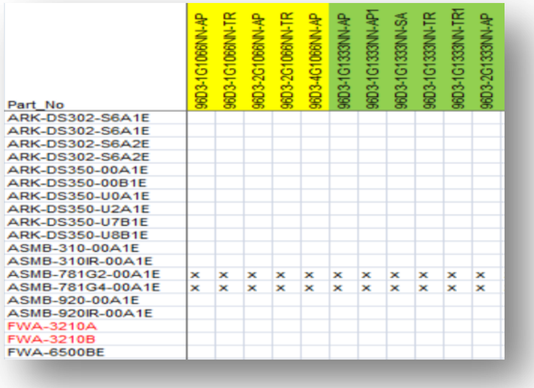


Motherboard Team DOA Testing Result

Memory Compatibility Testing Result

Check & Compare

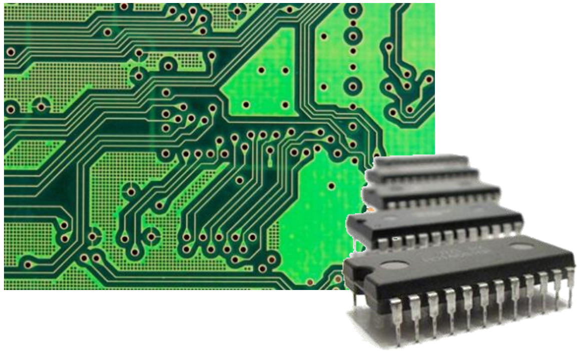
Both Teams Testing Result to Ensure M/B vs. Memory Compatibility



Part_No	96D3-1G1066NN-AP	96D3-1G1066NN-TR	96D3-2G1066NN-AP	96D3-2G1066NN-TR	96D3-4G1066NN-AP	96D3-1G1333NN-AP	96D3-1G1333NN-AP1	96D3-1G1333NN-SA	96D3-1G1333NN-TR	96D3-1G1333NN-TR1	96D3-2G1333NN-AP
ARK-DS302-S6A1E											
ARK-DS302-S6A1E											
ARK-DS302-S6A2E											
ARK-DS302-S6A2E											
ARK-DS350-00A1E											
ARK-DS350-00B1E											
ARK-DS350-U0A1E											
ARK-DS350-U2A1E											
ARK-DS350-U7B1E											
ARK-DS350-U8B1E											
ASMB-310-00A1E											
ASMB-310IR-00A1E											
ASMB-781G2-00A1E	x	x	x	x	x	x	x	x	x	x	x
ASMB-781G4-00A1E	x	x	x	x	x	x	x	x	x	x	x
ASMB-920-00A1E											
ASMB-920IR-00A1E											
FWA-3210A											
FWA-3210B											
FWA-6500BE											

Locked BOM

- IC Spec
- PCB Layout

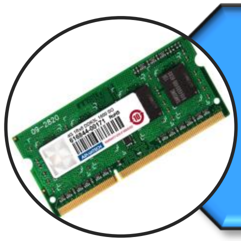


Minimum

3 Years Longevity

Every ADVATECH QUALIFIED DIMM (AQD) is back up by life-time warranty.

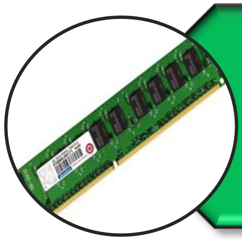
AQD Product Portfolio



Unbuffered DIMM

* General IPC Applications

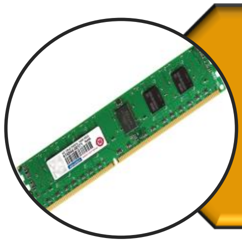
* 1GB, 2GB, 4GB & 8GB



ECC Unbuffered DIMM

* Improve system productivity and efficiency

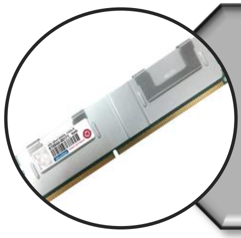
* 4GB & 8GB



Registered DIMM

* Providing the best solution for capacity and performance requirement.

* 8 GB & 16GB



Load Reduce DIMM

* Providing the biggest capacity per server with the lowest energy costs

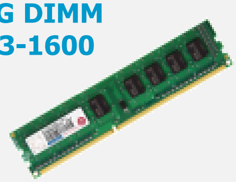
* 32GB

AQD Products Offering

LONG & SHORT Unbuffered DIMM

LONG DIMM
DDR3-1333
1G

AQD-D31GN13-SX



LONG DIMM
DDR3-1600
2G

AQD-D3L2GN16-SQ

LONG DIMM
DDR3-1600
4G

AQD-D3L4GN16-SQ

LONG DIMM
DDR3-1600
8G

AQD-D3L8GN16-SQ

SHORT DIMM
DDR3-1333
1G

AQD-SD31GN13-SX

SHORT DIMM
DDR3-1600
2G

AQD-SD3L2GN16-SQ

SHORT DIMM
DDR3-1600
4G

AQD-SD3L4GN16-SG

SHORT DIMM
DDR3-1600
8G

AQD-SD3L8GN16-SG

ECC Unbuffered DIMM

LONG DIMM
DDR3-1600
4G

AQD-D3L4GE16-SG

LONG DIMM
DDR3-1600
8G

AQD-D3L8GE16-SG

Registered DIMM

LONG DIMM
DDR3-1600
8G

AQD-D3L8GRV16-SG

LONG DIMM
DDR3-1600
16GB

AQD-D3L16RV16-SM

Load Reduce DIMM

DDR3-1333
32G

AQD-D3L32L13-SM

Part Number Decoder

A Q D – S D 3 L 2 G N V 1 6 – S G

PRODUCT NAME
A=Advantech
Q=Qualified
D=DIMM

TYPE
DM=SDRAM DIMM
DR=DDR
D2=DDR2
D3=DDR3
SS=SDRAM SO-DIMM
SD=DDR SO-DIMM
SD2=DDR2 SO-DIMM
SD3=DDR3 SO-DIMM

VOLTAGE
Blank= 1.5V
L=1.35V
U=1.25V

CAPACITY
1G=1GB
2G=2GB
4G=4GB
8G=8GB
16 =16GB
32 =32GB
64= 64GB

ADVNCED FEATURE
N= NON-ECC and NON REGISTER
R= REGISTER
E= ECC ONLY
L=Load reduce

Height
V= VLP

SPEED
40=400Mt/s
53=533Mt/s
66=667Mt/s
80=800Mt/s
10=1066Mt/s
13=1333Mt/s
16=1600Mt/s
18=1866Mt/s

FAB
S=Samsung
H=Hynix
M=Micron /Elpida
N=Nanya

VERSION
X=1Gb(128Mx8)
T=1Gb(256Mx4)
Q=2Gb(256Mx8)
Y=2Gb(512Mx4)
G=4Gb(512Mx8)
Z= 4Gb(1Gbx4)
M=8Gb(2Gbx4)

Color / Symbol Key

■ **Available** ■ **Phasing-out** ■ **Planning**

E **ECC** **R** **Registered** **F** **Fully Buffered** **N** **New**

LR **Load-Reduce** **V** **Very Low-Profile** **W** **Wide Temperature** **LV** **Low-Voltage**

AQD DDR3 Memory Modules Portfolio

DDR3
1.35 Low Voltage

		1333		1600	
		LONG	SHORT	LONG	SHORT
U-DIMM	1GB (128X8)	AQD-D31GN13-SX (1.5V)	AQD-SD31GN13-SX (1.5V)		
	2GB (256MX8)			AQD-D3L2GN16-SQ	AQD-SD3L2GN16-SQ
	4GB (512MX8)			AQD-D3L4GN16-SG	AQD-SD3L4GN16-SG
	8GB (512MX8)			AQD-D3L8GN16-SG	AQD-SD3L8GN16-SG
ECC U-DIMM	4GB (512MX8)			AQD-D3L4GE16-SG	
	8GB (512MX8)			AQD-D3L8GE16-SG	
R-DIMM	4GB (512MX8)				
	8GB (512MX8)			AQD-D3L8GRV16-SG	
	16GB(2Gbx4)			AQD-D3L16RV16-SM	
LOAD REDUCE	32GB (2GbX4)	AQD-D3L32L13-SM			

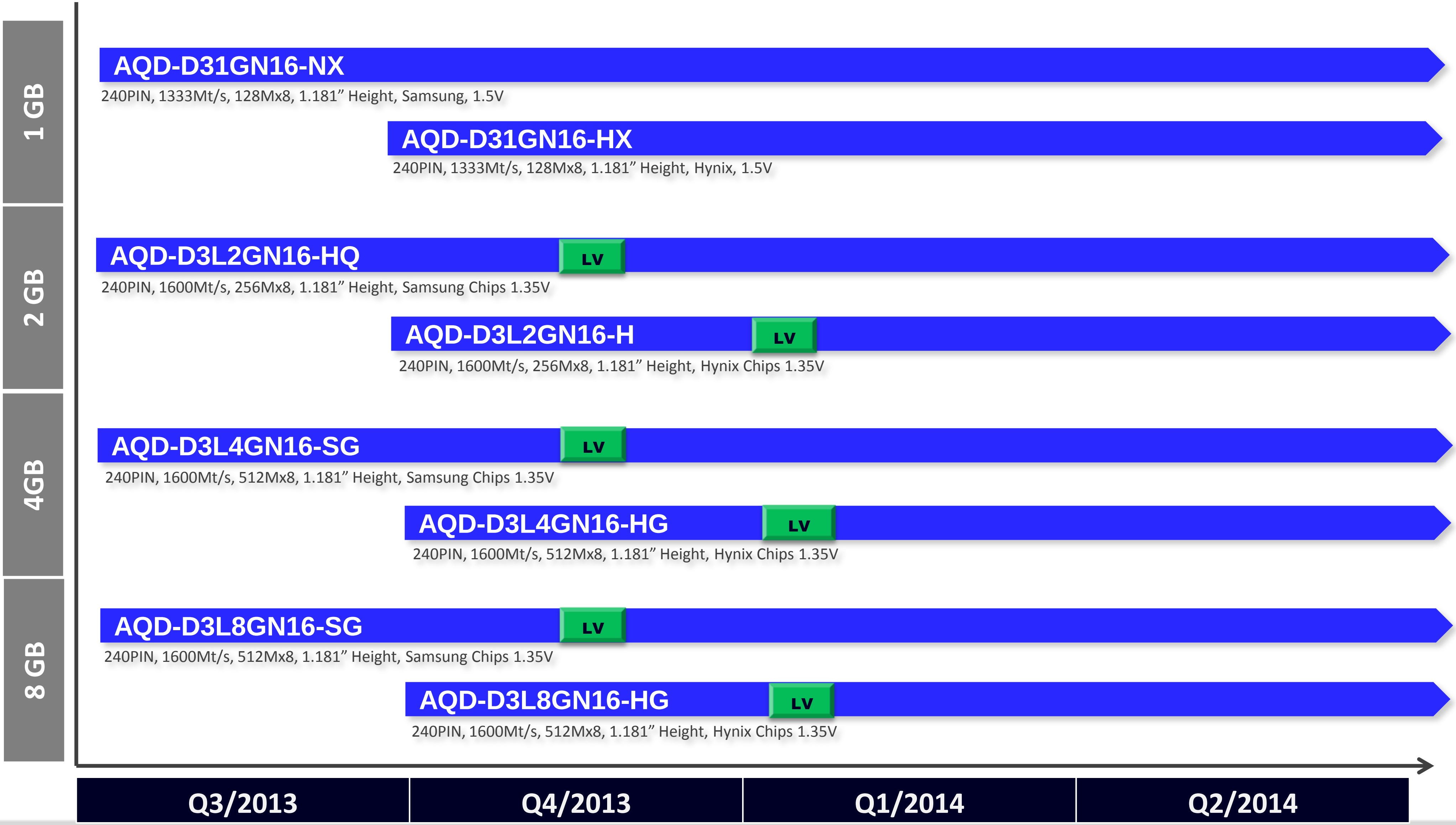
U-DIMM | ECC U-DIMM | R-DIMM | Load Reduce

🟨 Available ⬜ Phasing-out 🟨 Planning

E ECC R Registered F Fully Buffered N New

LR Load-Reduce V Very Low-Profile W Wide Temperature LV Low-Voltage

DDR3 DIMM



AQD-D31GN16-NX
240PIN, 1333Mt/s, 128Mx8, 1.181" Height, Samsung, 1.5V

AQD-D31GN16-HX
240PIN, 1333Mt/s, 128Mx8, 1.181" Height, Hynix, 1.5V

AQD-D3L2GN16-HQ
240PIN, 1600Mt/s, 256Mx8, 1.181" Height, Samsung Chips 1.35V

AQD-D3L2GN16-H
240PIN, 1600Mt/s, 256Mx8, 1.181" Height, Hynix Chips 1.35V

AQD-D3L4GN16-SG
240PIN, 1600Mt/s, 512Mx8, 1.181" Height, Samsung Chips 1.35V

AQD-D3L4GN16-HG
240PIN, 1600Mt/s, 512Mx8, 1.181" Height, Hynix Chips 1.35V

AQD-D3L8GN16-SG
240PIN, 1600Mt/s, 512Mx8, 1.181" Height, Samsung Chips 1.35V

AQD-D3L8GN16-HG
240PIN, 1600Mt/s, 512Mx8, 1.181" Height, Hynix Chips 1.35V

U-DIMM | ECC U-DIMM | R-DIMM | Load Reduce

🟨 Available ⬜ Phasing-out 🟧 Planning

E ECC R Registered F Fully Buffered N New

LR Load-Reduce V Very Low-Profile W Wide Temperature LV Low-Voltage

DDR3 SO-DIMM

1 GB

AQD-SD31GN16-SX
204PIN, 1333Mt/s, 128Mx8, 1.181” Height, Samsung Chips 1.5V

AQD-SD31GN16-HX
204PIN, 1333Mt/s, 128Mx8, 1.181” Height, Hynix Chips 1.5V

2 GB

AQD-SD3L2GN16-SQ LV
204PIN, 1600Mt/s, 256Mx8, 1.181” Height, Samsung Chips 1.35V

AQD-SD3L2GN16-HQ LV
204PIN, 1600Mt/s, 256Mx8, 1.181” Height, Hynix, Chips 1.35V

4GB

AQD-SD3L4GN16-SG LV
204PIN, 1600Mt/s, 512Mx8, 1.181” Height, Samsung Chips 1.35V

AQD-SD3L4GN16-HG LV
204PIN, 1600s, 512Mx8, 1.181” Height, Hynix Chips 1.35V

8 GB

AQD-SD3L8GN16-SG LV
204PIN, 1600Mt/s, 512Mx8, 1.181” Height, Samsung, Chips 1.35V

AQD-SD3L8GN16-HG LV
204PIN, 1600Mt/s, 512Mx8, 1.181” Height, Hynix, Chips 1.35V

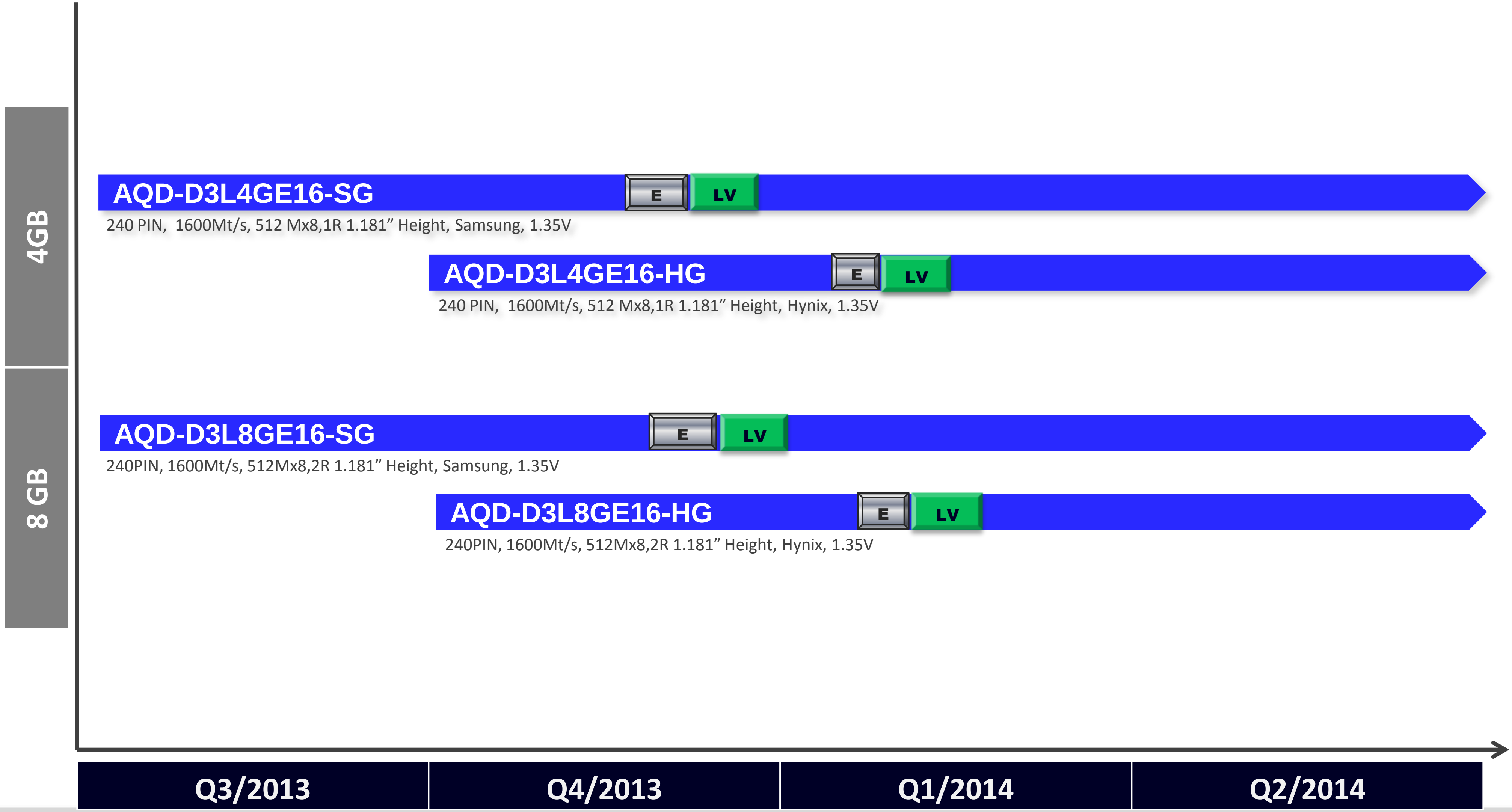
DDR3 DIMM Advance Feature

🟨 Available ▨ Phasing-out 🟧 Planning

E ECC R Registered F Fully Buffered N New

LR Load-Reduce V Very Low-Profile W Wide Temperature LV Low-Voltage

ECC



4GB

AQD-D3L4GE16-SG E LV

240 PIN, 1600Mt/s, 512 Mx8,1R 1.181” Height, Samsung, 1.35V

AQD-D3L4GE16-HG E LV

240 PIN, 1600Mt/s, 512 Mx8,1R 1.181” Height, Hynix, 1.35V

8 GB

AQD-D3L8GE16-SG E LV

240PIN, 1600Mt/s, 512Mx8,2R 1.181” Height, Samsung, 1.35V

AQD-D3L8GE16-HG E LV

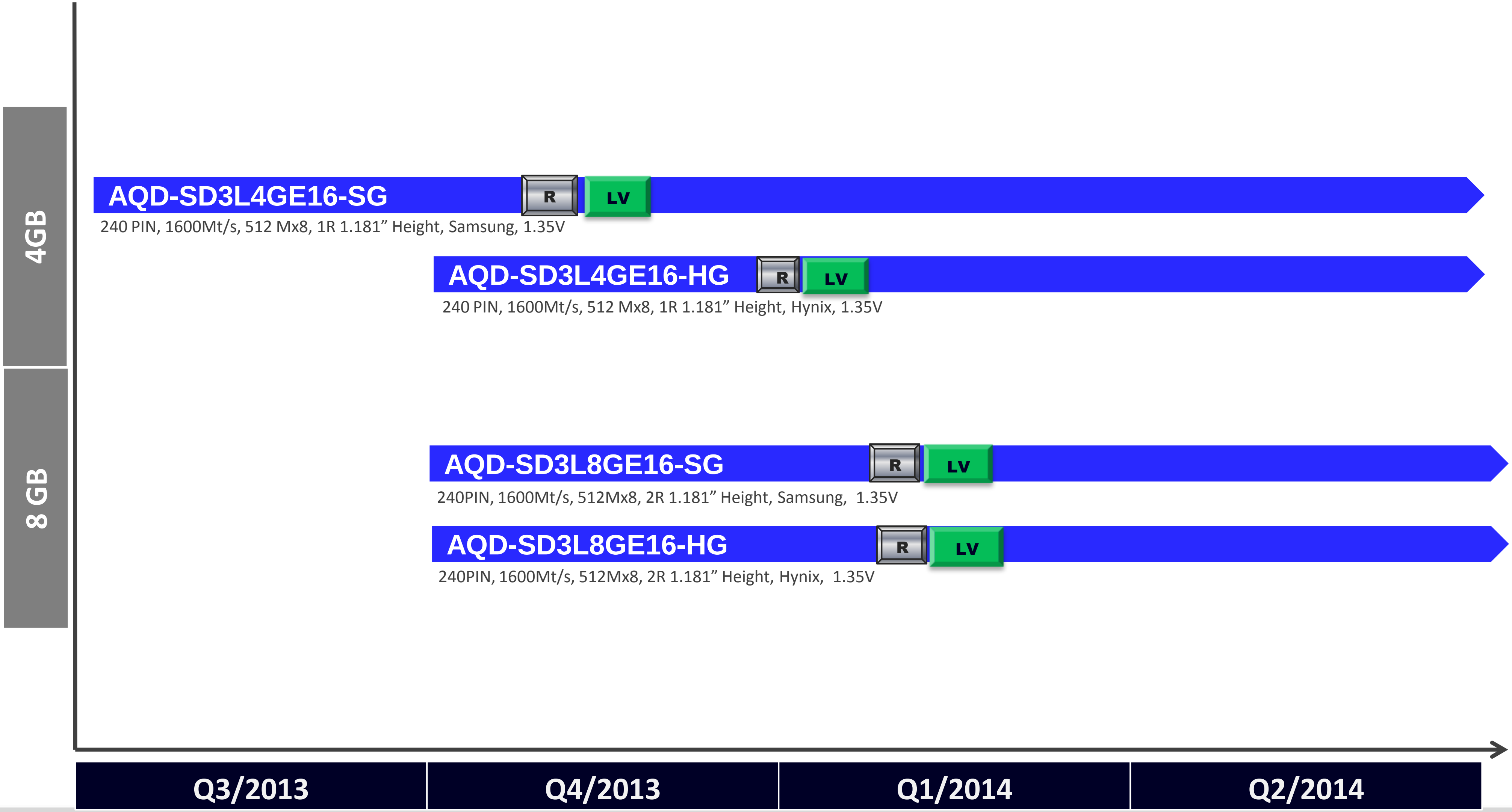
240PIN, 1600Mt/s, 512Mx8,2R 1.181” Height, Hynix, 1.35V

🟨 Available ▨ Phasing-out 🟧 Planning

E ECC
R Registered
F Fully Buffered
N New
LR Load-Reduce
V Very Low-Profile
W Wide Temperature
LV Low-Voltage

DDR3 SO DIMM Advance Feature

ECC



AQD-SD3L4GE16-SG
240 PIN, 1600Mt/s, 512 Mx8, 1R 1.181” Height, Samsung, 1.35V

AQD-SD3L4GE16-HG
240 PIN, 1600Mt/s, 512 Mx8, 1R 1.181” Height, Hynix, 1.35V

AQD-SD3L8GE16-SG
240PIN, 1600Mt/s, 512Mx8, 2R 1.181” Height, Samsung, 1.35V

AQD-SD3L8GE16-HG
240PIN, 1600Mt/s, 512Mx8, 2R 1.181” Height, Hynix, 1.35V

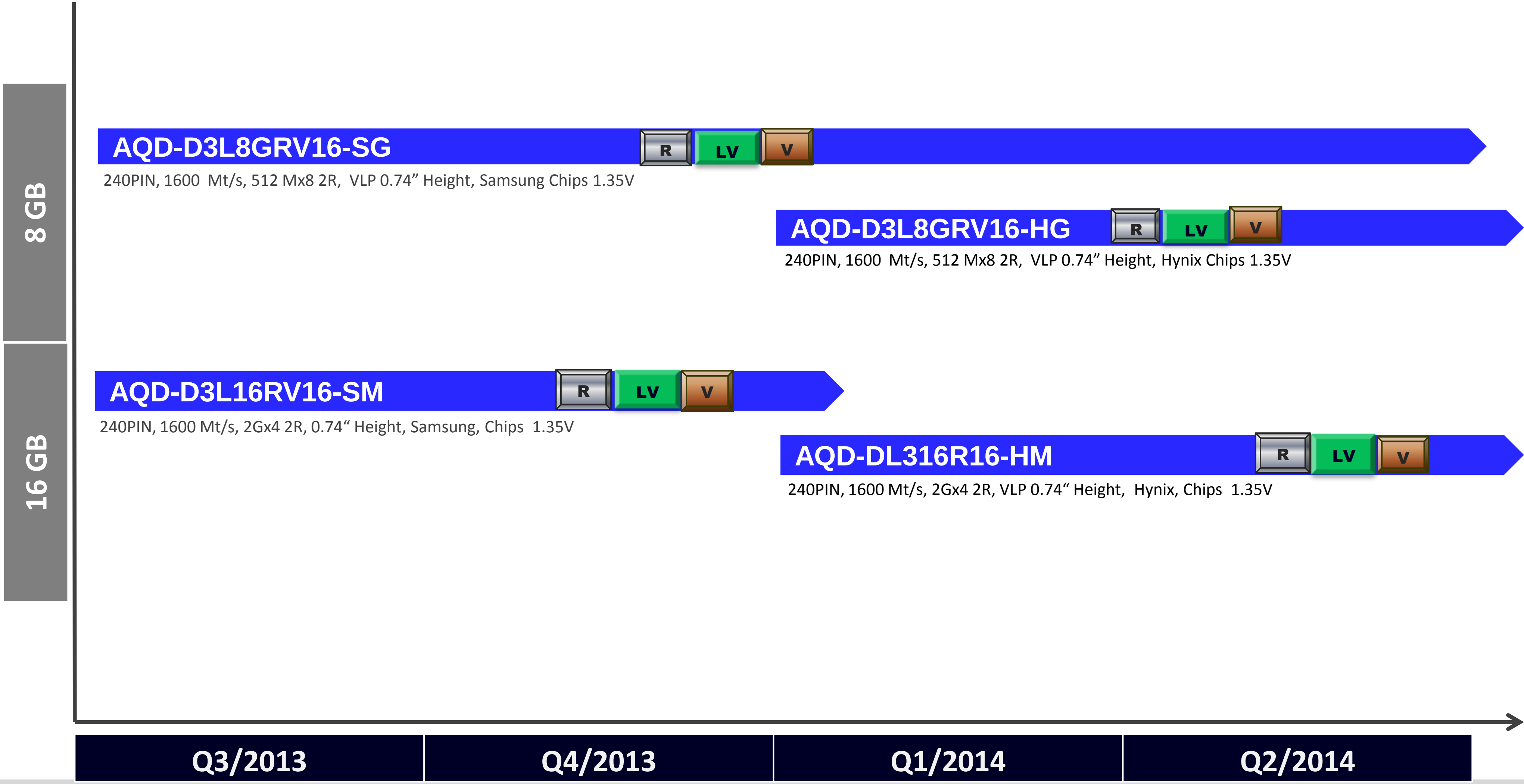
🟨 Available ⬜ Phasing-out 🟧 Planning

E ECC R Registered F Fully Buffered N New

LR Load-Reduce V Very Low-Profile W Wide Temperature LV Low-Voltage

DDR3 DIMM Advance Feature

ECC and Registered



AQD-D3L8GRV16-SG

240PIN, 1600 Mt/s, 512 Mx8 2R, VLP 0.74” Height, Samsung Chips 1.35V

AQD-D3L8GRV16-HG

240PIN, 1600 Mt/s, 512 Mx8 2R, VLP 0.74” Height, Hynix Chips 1.35V

AQD-D3L16RV16-SM

240PIN, 1600 Mt/s, 2Gx4 2R, 0.74“ Height, Samsung, Chips 1.35V

AQD-DL316R16-HM

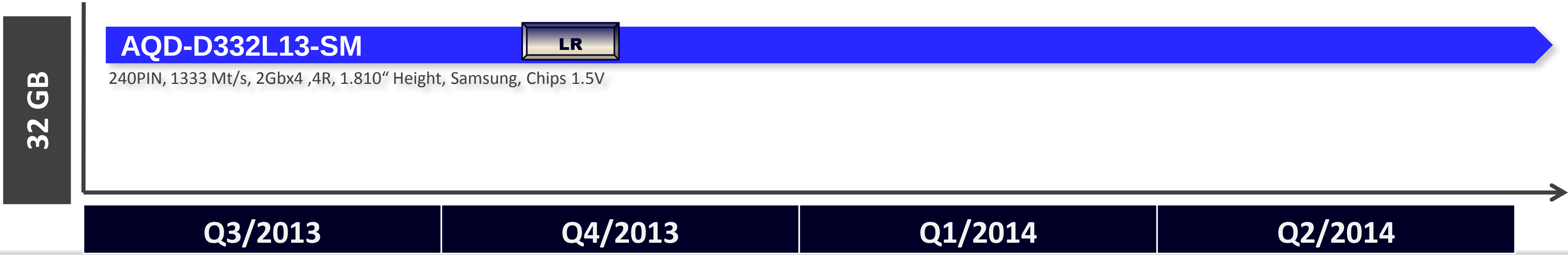
240PIN, 1600 Mt/s, 2Gx4 2R, VLP 0.74“ Height, Hynix, Chips 1.35V

🟨 Available ⬜ Phasing-out 🟨 Planning

E ECC
R Registered
F Fully Buffered
N New
LR Load-Reduce
V Very Low-Profile
W Wide Temperature
LV Low-Voltage

DDR3 DIMM Advance Feature

Load Reduce



AQD-D332L13-SM

240PIN, 1333 Mt/s, 2Gbx4 ,4R, 1.810" Height, Samsung, Chips 1.5V

PART II,

96 PARTS MEMORY MODULE

Part Number Decoder

9 6 D M – 6 4 M 1 0 0 N N – A P

Memory Type

DM=SDRAM DIMM
DR=DDR
DRI=INDUSTRIAL GRADE DDR
D2=DDR2
D2I=INDUSTRIAL GRADE DDR2
D3=DDR3
SS=SDRAM SO-DIMM
SD=DDR SO-DIMM
SDI=INDUSTRIAL GRADE SO-DDR
SD2=DDR2 SO-DIMM
SD2I=INDUSRIAL GRADE SO-DDR2
SD3=DDR3 SO-DIMM
SD3I=INDUSTRIAL GRADE SO-DDR3

Capacity

64M=64MB
128M=128MB
256M=256MB
512M=512MB
1G=1GB
2G=2GB
4G=4GB
8G=8GB

Speed

100=100Mb/s
133=133Mb/s
266=266Mb/s
333=333Mb/s
400=400Mb/s
533=533Mb/s
667=667Mb/s
800=800Mb/s
1066=1066Mb/s
1333=1333Mbs

Advance Feature

NN=
NON-ECC and NON-REGISTER
ER=
ECC AND REGISTER
E=
ECC ONLY

Manufacturer

AP=APACER
ATL=ATP
DA=DATA
IK=INNODISK
KI=KINGSTON
MI=MIRCON
SB=SWISSBIT
TR=TRANSCEND
VI=VIRTIUM

Color / Symbol Key

■ Available ■ Phasing-out □ Planning

E ECC R Registered F Fully Buffered N New

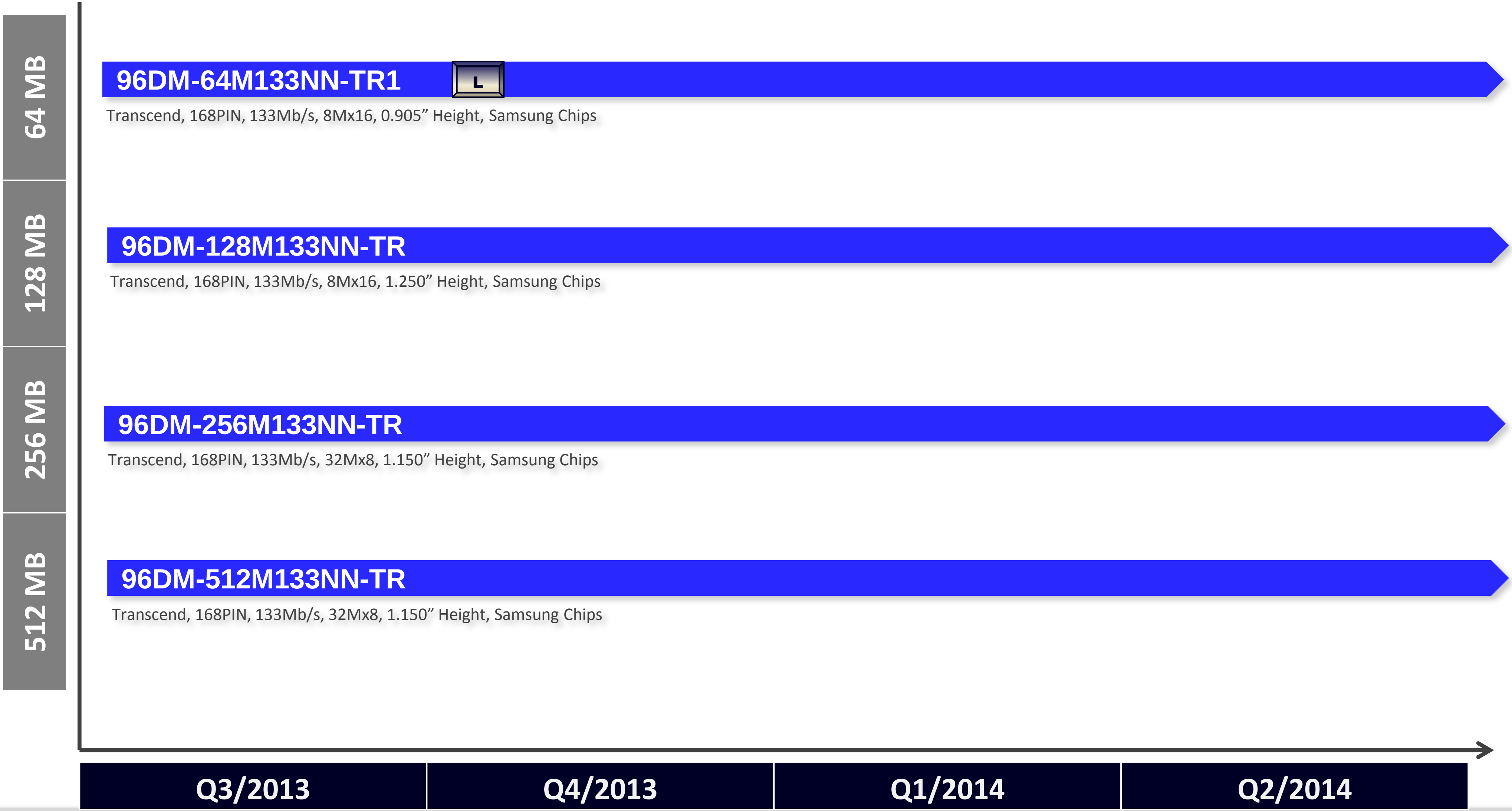
L Low-Profile V Very Low-Profile W Wide Temperature

SDRAM DIMM

🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



64 MB

96DM-64M133NN-TR1 L

Transcend, 168PIN, 133Mb/s, 8Mx16, 0.905” Height, Samsung Chips

128 MB

96DM-128M133NN-TR

Transcend, 168PIN, 133Mb/s, 8Mx16, 1.250” Height, Samsung Chips

256 MB

96DM-256M133NN-TR

Transcend, 168PIN, 133Mb/s, 32Mx8, 1.150” Height, Samsung Chips

512 MB

96DM-512M133NN-TR

Transcend, 168PIN, 133Mb/s, 32Mx8, 1.150” Height, Samsung Chips

Q3/2013	Q4/2013	Q1/2014	Q2/2014

SDRAM SO-DIMM

🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

64 MB

96SS-64M133NN-TR L

Transcend, 144PIN, 133Mb/s, 8Mx16, 0.945” Height, Samsung Chips

128 MB

96SS-128M133NN-TR

Transcend, 144PIN, 133Mb/s, 8Mx16, 1.150” Height, Samsung Chips

96SS-128M133NN-TR1 L

Transcend, 144PIN, 133Mb/s, 16Mx16, 0.945” Height, Samsung Chips

256 MB

96SS-256M133NN-TR

Transcend, 144PIN, 133Mb/s, 16Mx16, 1.250” Height, Samsung Chips

96SS-256M133NN-TR3

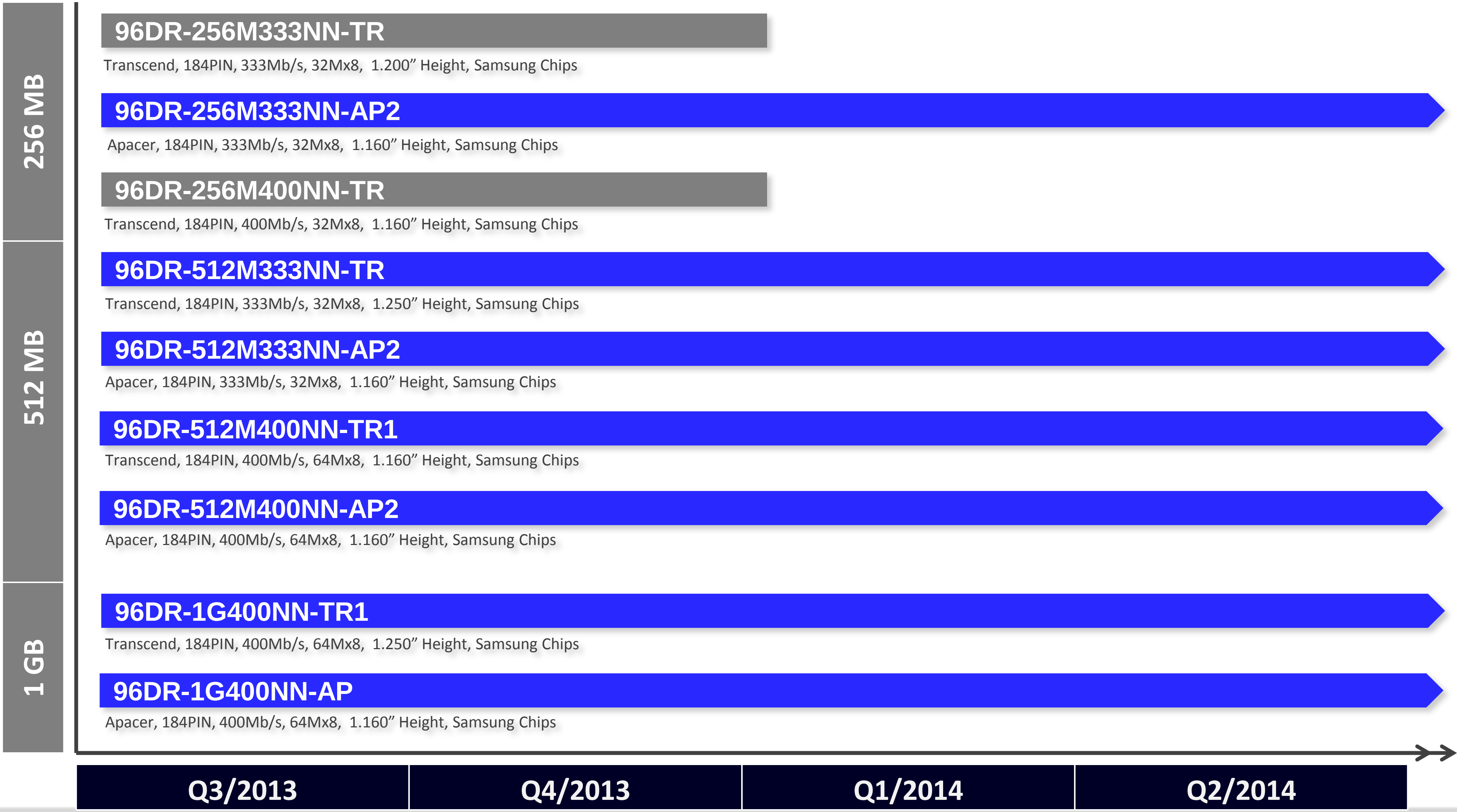
Transcend, 144PIN, 133Mb/s, 32Mx8, 1.150” Height, Samsung Chips

DDR DIMM

🟦 Available ▨ Phasing-out 🟦 Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



256 MB

96DR-256M333NN-TR

Transcend, 184PIN, 333Mb/s, 32Mx8, 1.200” Height, Samsung Chips

96DR-256M333NN-AP2

Apacer, 184PIN, 333Mb/s, 32Mx8, 1.160” Height, Samsung Chips

96DR-256M400NN-TR

Transcend, 184PIN, 400Mb/s, 32Mx8, 1.160” Height, Samsung Chips

512 MB

96DR-512M333NN-TR

Transcend, 184PIN, 333Mb/s, 32Mx8, 1.250” Height, Samsung Chips

96DR-512M333NN-AP2

Apacer, 184PIN, 333Mb/s, 32Mx8, 1.160” Height, Samsung Chips

96DR-512M400NN-TR1

Transcend, 184PIN, 400Mb/s, 64Mx8, 1.160” Height, Samsung Chips

96DR-512M400NN-AP2

Apacer, 184PIN, 400Mb/s, 64Mx8, 1.160” Height, Samsung Chips

1 GB

96DR-1G400NN-TR1

Transcend, 184PIN, 400Mb/s, 64Mx8, 1.250” Height, Samsung Chips

96DR-1G400NN-AP

Apacer, 184PIN, 400Mb/s, 64Mx8, 1.160” Height, Samsung Chips

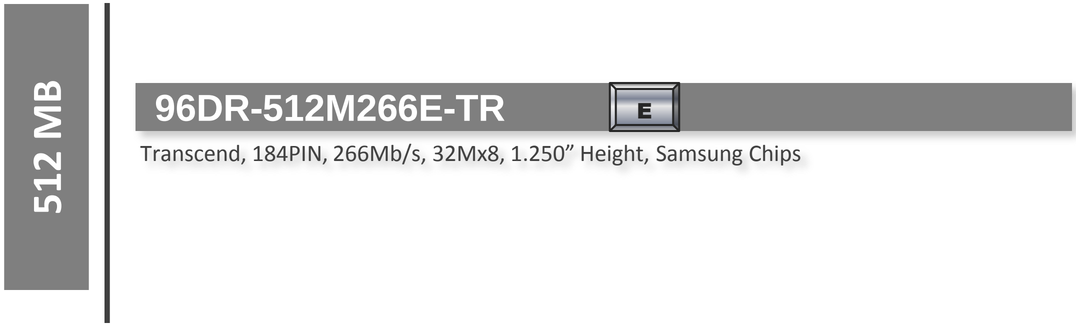
🟦 Available ▨ Phasing-out ▭ Planning

E ECC **R** Registered **F** Fully Buffered **N** New

L Low-Profile **V** Very Low-Profile **W** Wide Temperature

DDR DIMM Advance Feature

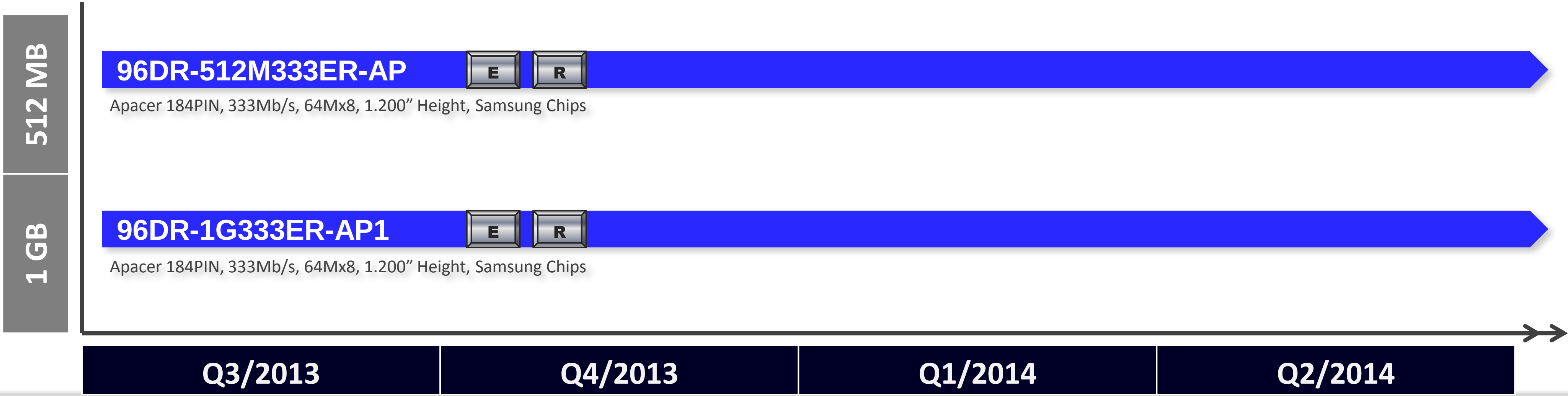
ECC



96DR-512M266E-TR

Transcend, 184PIN, 266Mb/s, 32Mx8, 1.250” Height, Samsung Chips

ECC and Registered



96DR-512M333ER-AP

Apacer 184PIN, 333Mb/s, 64Mx8, 1.200” Height, Samsung Chips

96DR-1G333ER-AP1

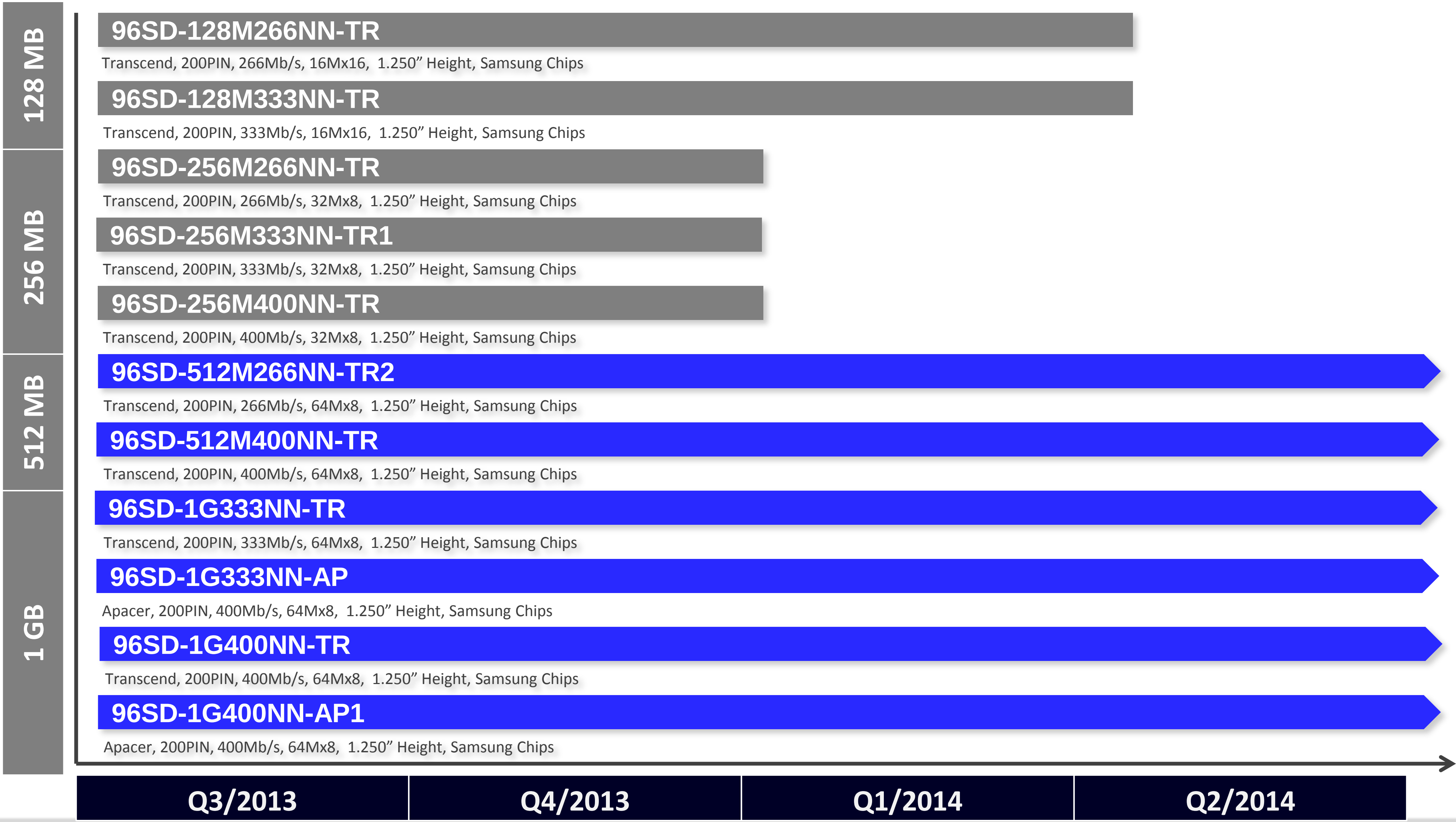
Apacer 184PIN, 333Mb/s, 64Mx8, 1.200” Height, Samsung Chips

DDR SO-DIMM

🟦 Available ▨ Phasing-out 🟦 Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



128 MB

96SD-128M266NN-TR

Transcend, 200PIN, 266Mb/s, 16Mx16, 1.250” Height, Samsung Chips

96SD-128M333NN-TR

Transcend, 200PIN, 333Mb/s, 16Mx16, 1.250” Height, Samsung Chips

256 MB

96SD-256M266NN-TR

Transcend, 200PIN, 266Mb/s, 32Mx8, 1.250” Height, Samsung Chips

96SD-256M333NN-TR1

Transcend, 200PIN, 333Mb/s, 32Mx8, 1.250” Height, Samsung Chips

96SD-256M400NN-TR

Transcend, 200PIN, 400Mb/s, 32Mx8, 1.250” Height, Samsung Chips

512 MB

96SD-512M266NN-TR2

Transcend, 200PIN, 266Mb/s, 64Mx8, 1.250” Height, Samsung Chips

96SD-512M400NN-TR

Transcend, 200PIN, 400Mb/s, 64Mx8, 1.250” Height, Samsung Chips

1 GB

96SD-1G333NN-TR

Transcend, 200PIN, 333Mb/s, 64Mx8, 1.250” Height, Samsung Chips

96SD-1G333NN-AP

Apacer, 200PIN, 400Mb/s, 64Mx8, 1.250” Height, Samsung Chips

96SD-1G400NN-TR

Transcend, 200PIN, 400Mb/s, 64Mx8, 1.250” Height, Samsung Chips

96SD-1G400NN-AP1

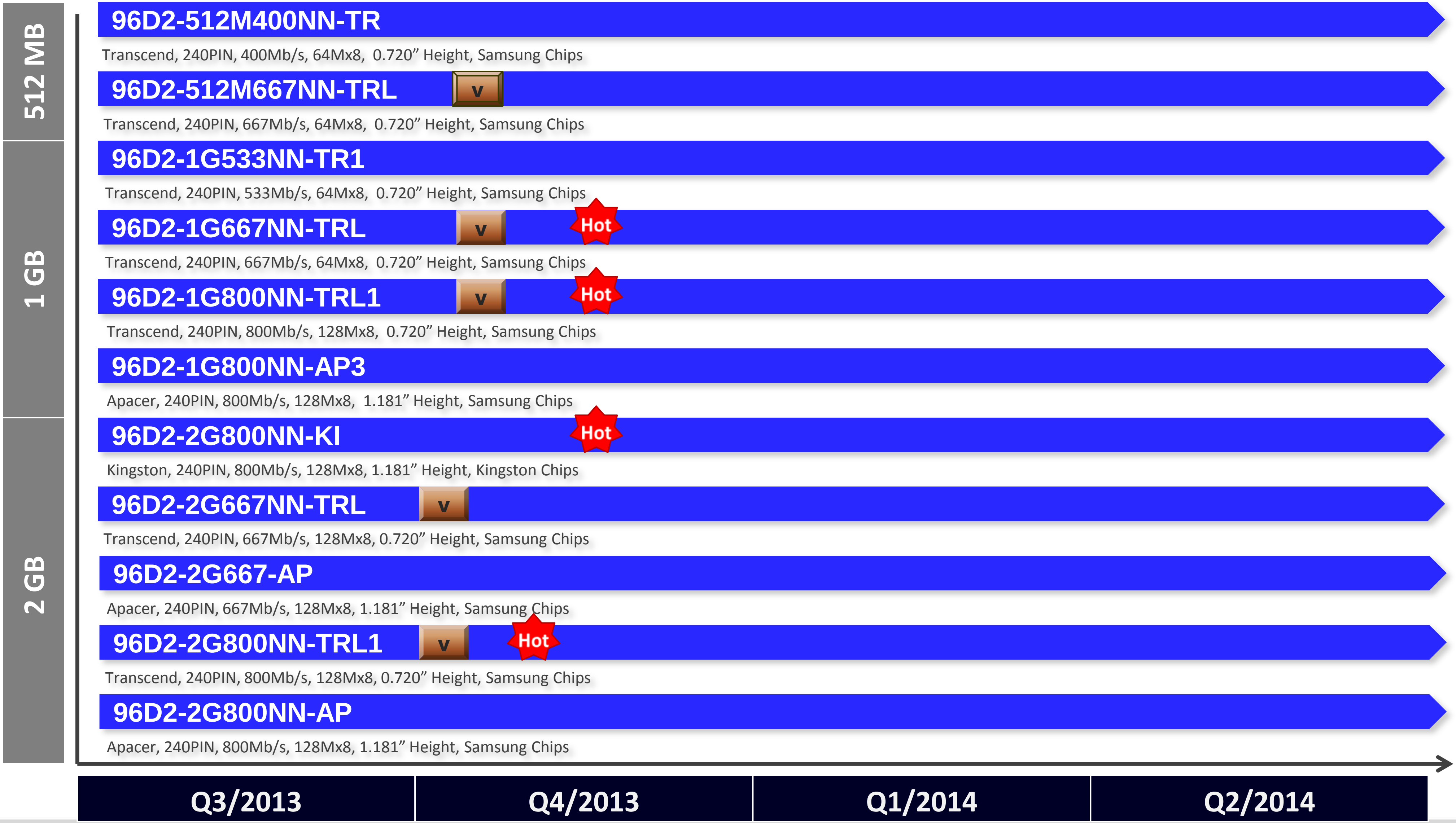
Apacer, 200PIN, 400Mb/s, 64Mx8, 1.250” Height, Samsung Chips

DDR2 DIMM

▬ Available ▬ Phasing-out ▬ Planning

E ECC **R** Registered **F** Fully Buffered **N** New

L Low-Profile **V** Very Low-Profile **W** Wide Temperature



	Part			Description
512 MB	**96D2-512M400NN-TR**			Transcend, 240PIN, 400Mb/s, 64Mx8, 0.720" Height, Samsung Chips
	96D2-512M667NN-TRL	V		Transcend, 240PIN, 667Mb/s, 64Mx8, 0.720" Height, Samsung Chips
1 GB	**96D2-1G533NN-TR1**			Transcend, 240PIN, 533Mb/s, 64Mx8, 0.720" Height, Samsung Chips
	96D2-1G667NN-TRL	V	Hot	Transcend, 240PIN, 667Mb/s, 64Mx8, 0.720" Height, Samsung Chips
	96D2-1G800NN-TRL1	V	Hot	Transcend, 240PIN, 800Mb/s, 128Mx8, 0.720" Height, Samsung Chips
	96D2-1G800NN-AP3			Apacer, 240PIN, 800Mb/s, 128Mx8, 1.181" Height, Samsung Chips
2 GB	**96D2-2G800NN-KI**		Hot	Kingston, 240PIN, 800Mb/s, 128Mx8, 1.181" Height, Kingston Chips
	96D2-2G667NN-TRL	V		Transcend, 240PIN, 667Mb/s, 128Mx8, 0.720" Height, Samsung Chips
	96D2-2G667-AP			Apacer, 240PIN, 667Mb/s, 128Mx8, 1.181" Height, Samsung Chips
	96D2-2G800NN-TRL1	V	Hot	Transcend, 240PIN, 800Mb/s, 128Mx8, 0.720" Height, Samsung Chips
	96D2-2G800NN-AP			Apacer, 240PIN, 800Mb/s, 128Mx8, 1.181" Height, Samsung Chips

Q3/2013	Q4/2013	Q1/2014	Q2/2014

DDR2 DIMM Advance Feature

🟦 Available ▨ Phasing-out ☐ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

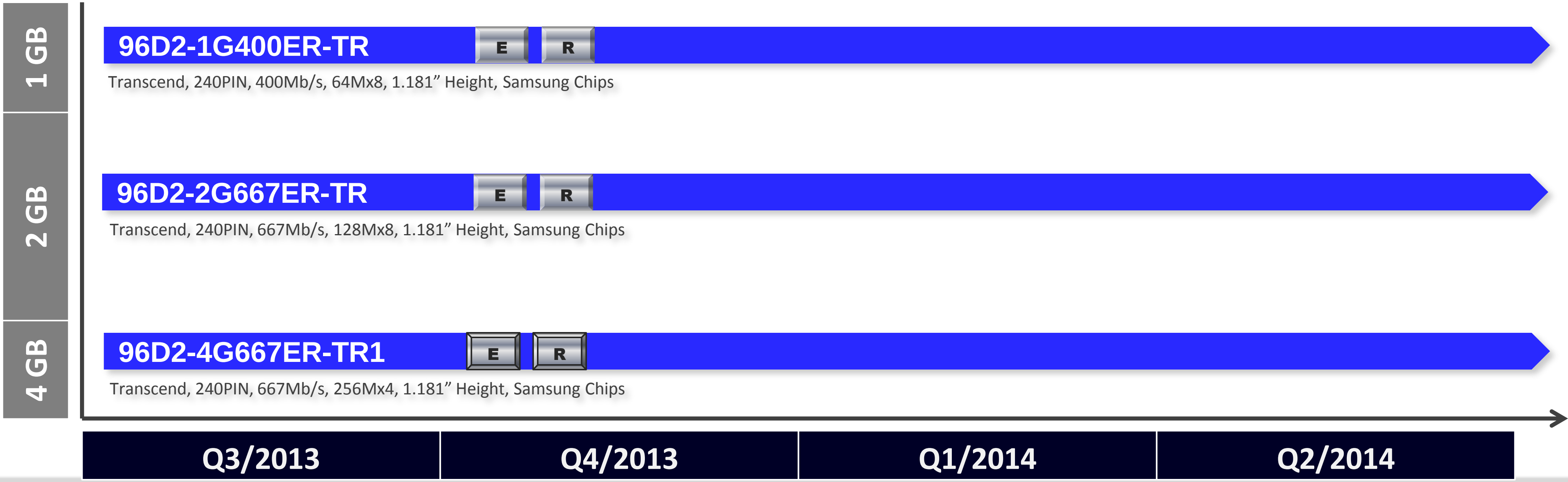
ECC

96D2-1G533E-TR: Transcend, 240PIN, 533Mb/s, 64Mx8, 1.181” Height, Samsung Chips

96D2-2G800E-AP1: Apacer, 240PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96D2-2G800E-TR1: Transcend, 240PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

ECC and Registered



96D2-1G400ER-TR: Transcend, 240PIN, 400Mb/s, 64Mx8, 1.181” Height, Samsung Chips

96D2-2G667ER-TR: Transcend, 240PIN, 667Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96D2-4G667ER-TR1: Transcend, 240PIN, 667Mb/s, 256Mx4, 1.181” Height, Samsung Chips

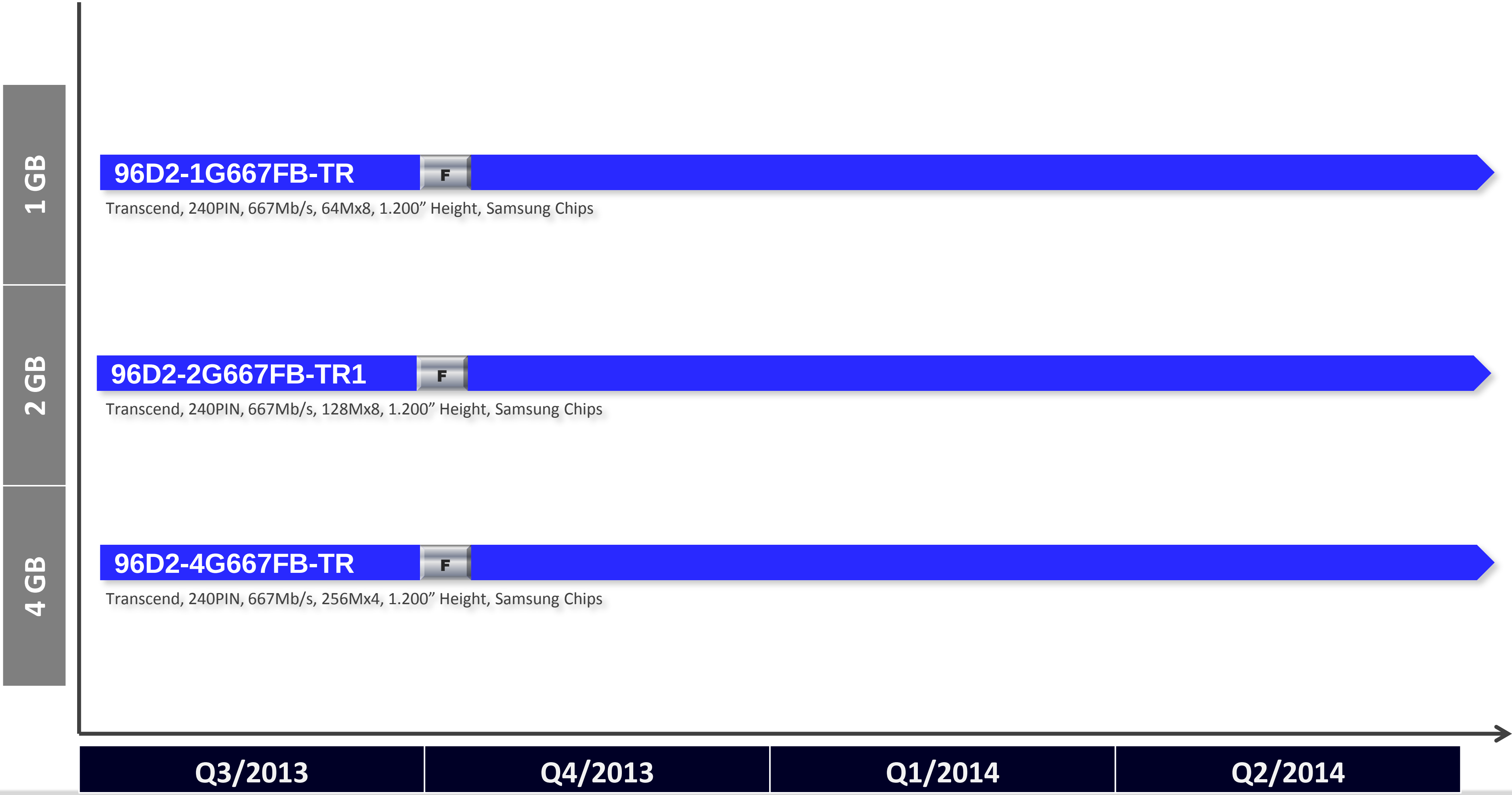
DDR2 DIMM Advance Feature

🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

Fully Buffered



96D2-1G667FB-TR

Transcend, 240PIN, 667Mb/s, 64Mx8, 1.200” Height, Samsung Chips

96D2-2G667FB-TR1

Transcend, 240PIN, 667Mb/s, 128Mx8, 1.200” Height, Samsung Chips

96D2-4G667FB-TR

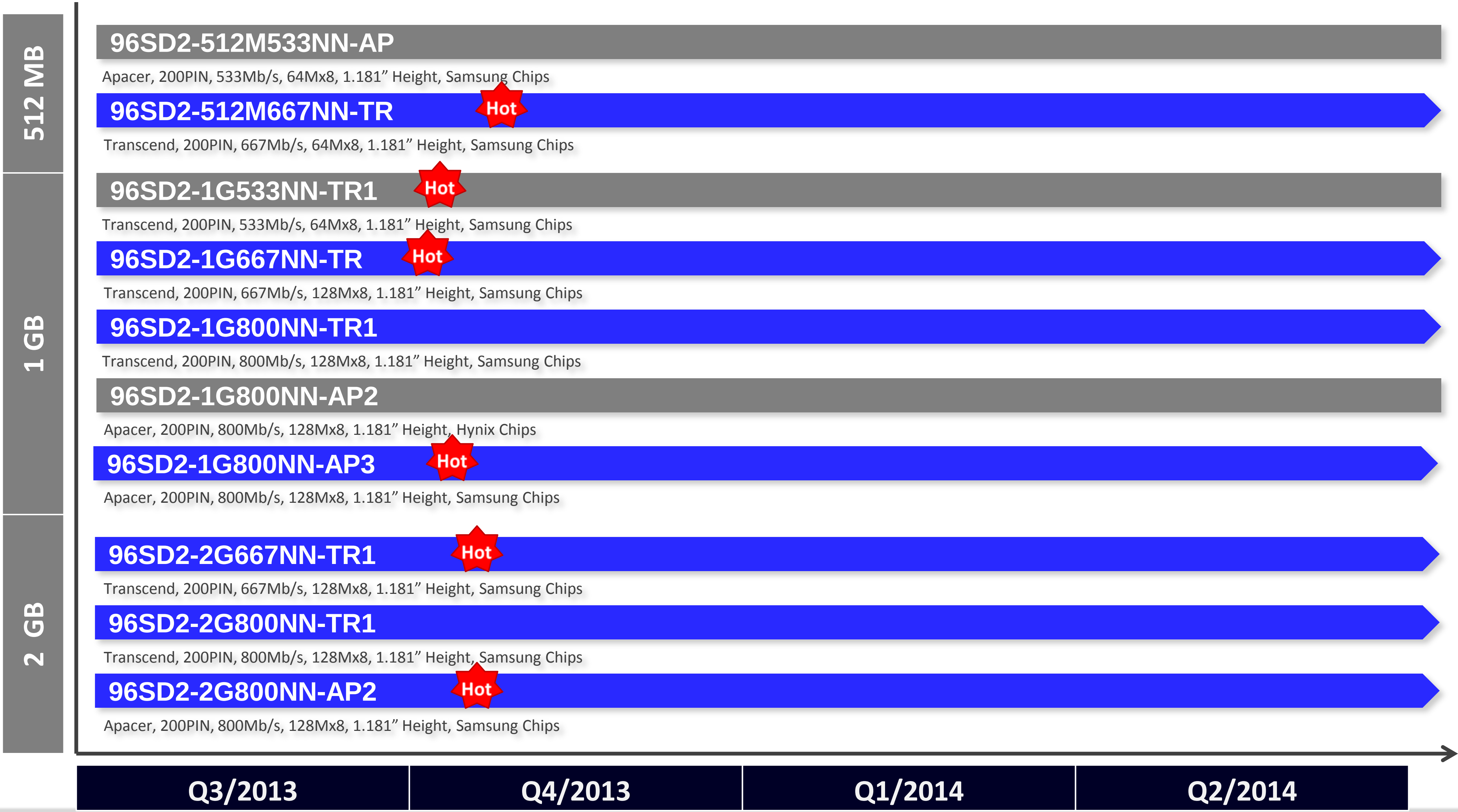
Transcend, 240PIN, 667Mb/s, 256Mx4, 1.200” Height, Samsung Chips

DDR2 SO-DIMM

🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



96SD2-512M533NN-AP
Apacer, 200PIN, 533Mb/s, 64Mx8, 1.181” Height, Samsung Chips

96SD2-512M667NN-TR Hot
Transcend, 200PIN, 667Mb/s, 64Mx8, 1.181” Height, Samsung Chips

96SD2-1G533NN-TR1 Hot
Transcend, 200PIN, 533Mb/s, 64Mx8, 1.181” Height, Samsung Chips

96SD2-1G667NN-TR Hot
Transcend, 200PIN, 667Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96SD2-1G800NN-TR1
Transcend, 200PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96SD2-1G800NN-AP2
Apacer, 200PIN, 800Mb/s, 128Mx8, 1.181” Height, Hynix Chips

96SD2-1G800NN-AP3 Hot
Apacer, 200PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96SD2-2G667NN-TR1 Hot
Transcend, 200PIN, 667Mb/s, 128Mx8, 1.181” Height, Samsung Chips

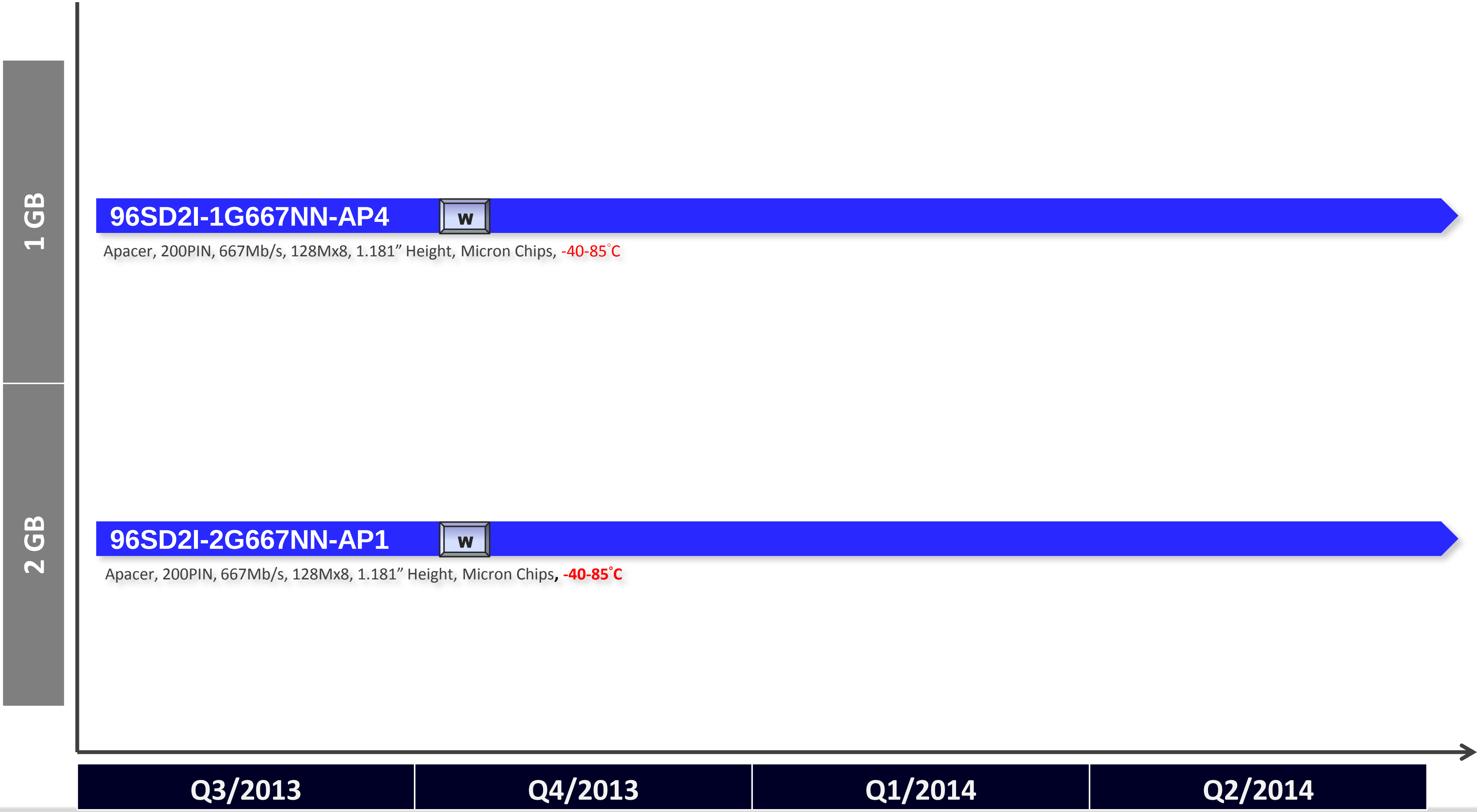
96SD2-2G800NN-TR1
Transcend, 200PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96SD2-2G800NN-AP2 Hot
Apacer, 200PIN, 800Mb/s, 128Mx8, 1.181” Height, Samsung Chips

DDR2 SO-DIMM **Wide Temp.**

🟦 Available ▨ Phasing-out ▭ Planning

E ECC
R Registered
F Fully Buffered
N New
L Low-Profile
V Very Low-Profile
W Wide Temperature



1 GB

96SD2I-1G667NN-AP4 W

Apacer, 200PIN, 667Mb/s, 128Mx8, 1.181” Height, Micron Chips, -40-85˚C

2 GB

96SD2I-2G667NN-AP1 W

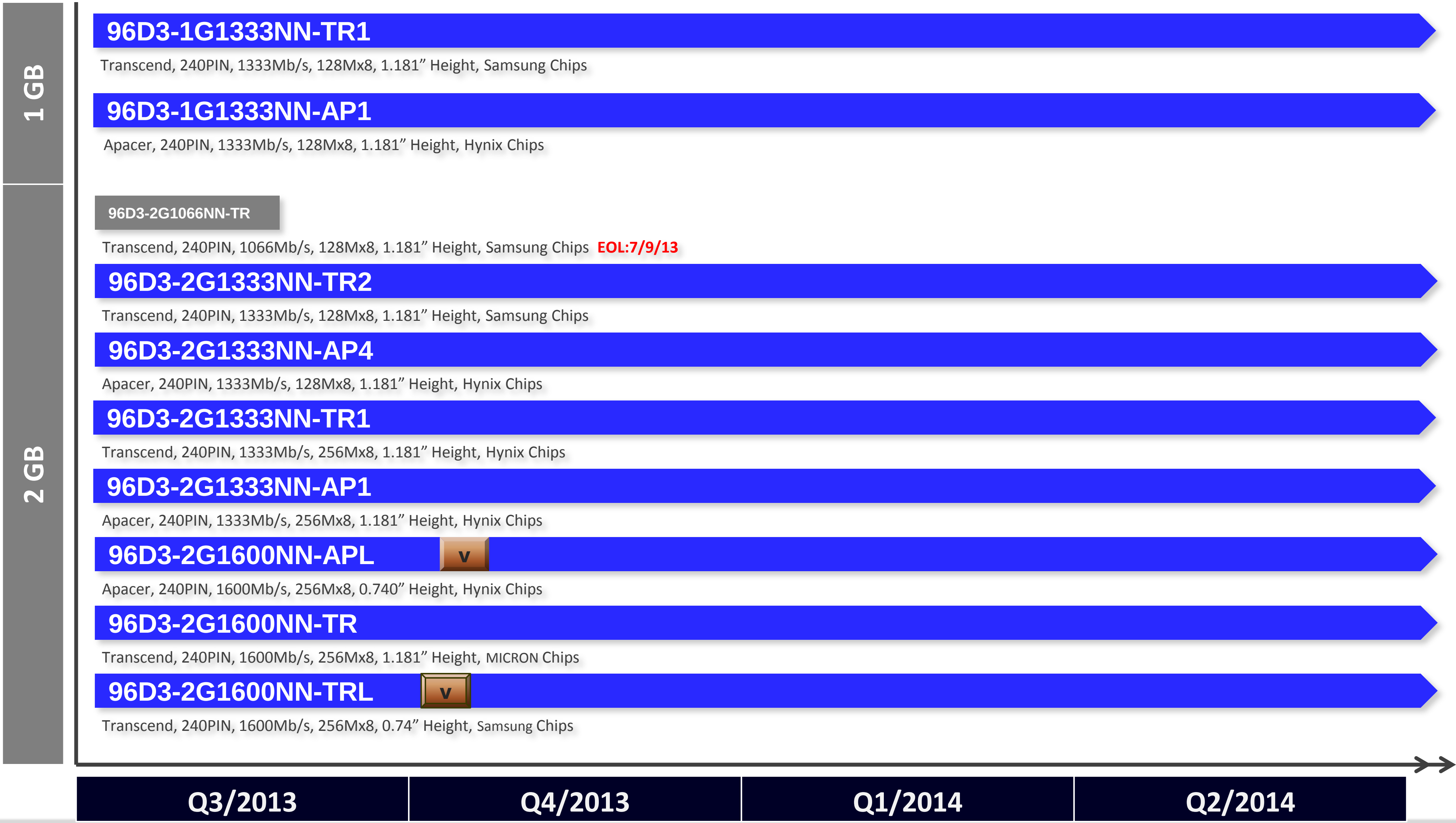
Apacer, 200PIN, 667Mb/s, 128Mx8, 1.181” Height, Micron Chips, **-40-85˚C**

Q3/2013	Q4/2013	Q1/2014	Q2/2014

🟦 Available ▨ Phasing-out 🟦 Planning

DDR3 DIMM

E ECC R Registered F Fully Buffered N New
L Low-Profile V Very Low-Profile W Wide Temperature



96D3-1G1333NN-TR1

Transcend, 240PIN, 1333Mb/s, 128Mx8, 1.181" Height, Samsung Chips

96D3-1G1333NN-AP1

Apacer, 240PIN, 1333Mb/s, 128Mx8, 1.181" Height, Hynix Chips

96D3-2G1066NN-TR

Transcend, 240PIN, 1066Mb/s, 128Mx8, 1.181" Height, Samsung Chips **EOL:7/9/13**

96D3-2G1333NN-TR2

Transcend, 240PIN, 1333Mb/s, 128Mx8, 1.181" Height, Samsung Chips

96D3-2G1333NN-AP4

Apacer, 240PIN, 1333Mb/s, 128Mx8, 1.181" Height, Hynix Chips

96D3-2G1333NN-TR1

Transcend, 240PIN, 1333Mb/s, 256Mx8, 1.181" Height, Hynix Chips

96D3-2G1333NN-AP1

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181" Height, Hynix Chips

96D3-2G1600NN-APL

Apacer, 240PIN, 1600Mb/s, 256Mx8, 0.740" Height, Hynix Chips

96D3-2G1600NN-TR

Transcend, 240PIN, 1600Mb/s, 256Mx8, 1.181" Height, MICRON Chips

96D3-2G1600NN-TRL

Transcend, 240PIN, 1600Mb/s, 256Mx8, 0.74" Height, Samsung Chips

DDR3 DIMM

🟦 Available ▨ Phasing-out 🟦 Planning

E ECC
R Registered
F Fully Buffered
N New
L Low-Profile
V Very Low-Profile
W Wide Temperature

96D3-4G1333NN-TR

Transcend, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96D3-4G1333NN-AP

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96D3-4G1600NN-APL

Apacer, 240PIN, 1600Mb/s, 256Mx8, 0.740” Height, Hynix Chips

96D3-4G1600NN-TR

Transcend, 240PIN, 1600Mb/s, 256Mx8, 1.181” Height, Micron Chips EOL:7/9/2013

96D3-4G1600NN-TR

Transcend, 240PIN, 1600Mb/s, 256Mx8, 1.181” Height, Samsung Chips

96D3-8G1333NN-APL

Apacer, 240PIN, 1333Mb/s, 512Mx8, 0.740” Height, Micron Chips

96D3-8G1600NN-APL

Apacer, 240PIN, 1600Mb/s, 512Mx8, 0.740” Height, Micron Chips

96D3-8G1600NN-TR

Transcend, 240PIN, 1600Mb/s, 512Mx8, 1.181” Height, Micron Chips

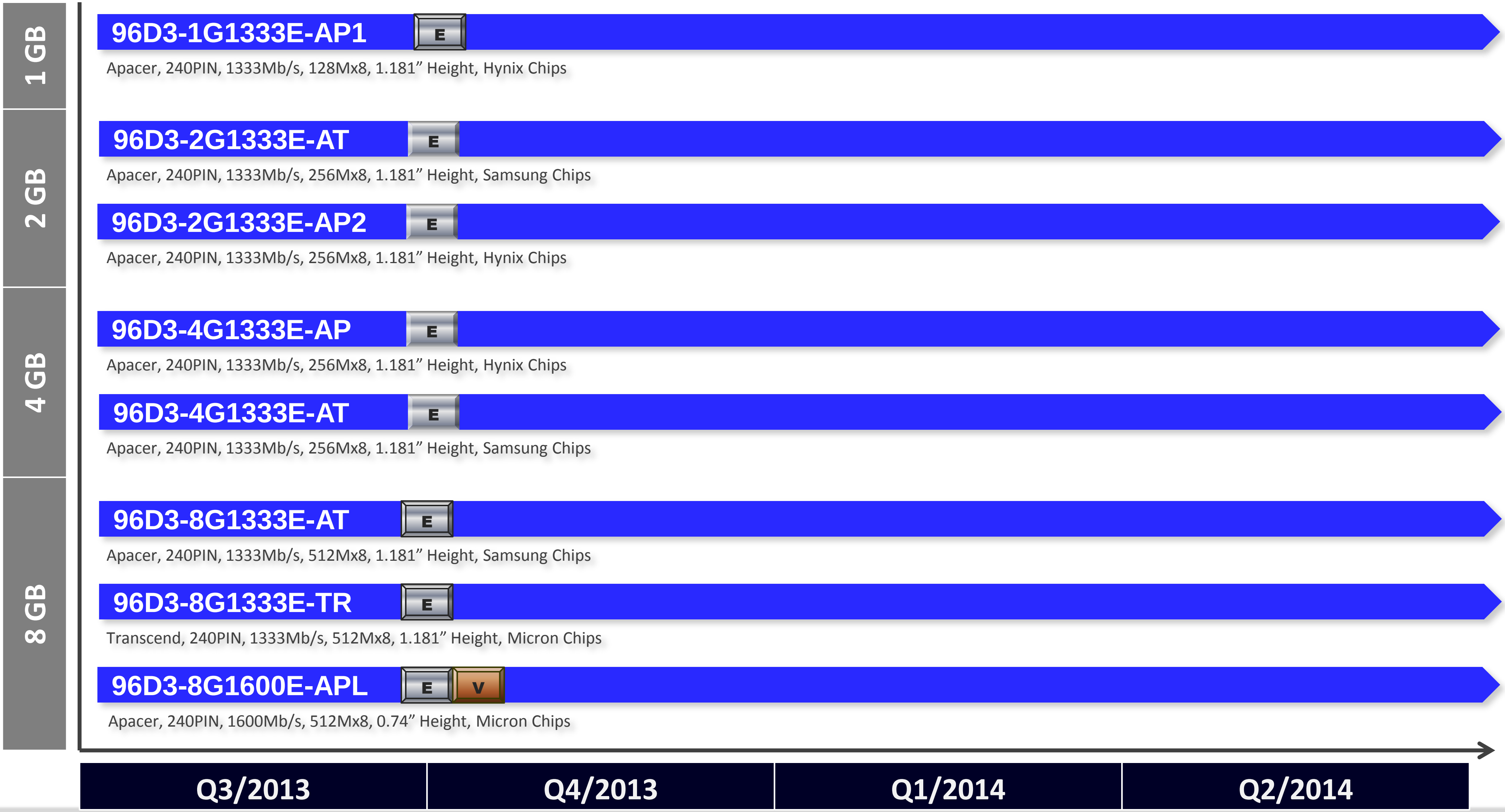
DDR3 DIMM Advance Feature

🟦 Available ⬜ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

ECC



1 GB

96D3-1G1333E-AP1 E

Apacer, 240PIN, 1333Mb/s, 128Mx8, 1.181” Height, Hynix Chips

2 GB

96D3-2G1333E-AT E

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Samsung Chips

96D3-2G1333E-AP2 E

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

4 GB

96D3-4G1333E-AP E

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96D3-4G1333E-AT E

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Samsung Chips

8 GB

96D3-8G1333E-AT E

Apacer, 240PIN, 1333Mb/s, 512Mx8, 1.181” Height, Samsung Chips

96D3-8G1333E-TR E

Transcend, 240PIN, 1333Mb/s, 512Mx8, 1.181” Height, Micron Chips

96D3-8G1600E-APL E V

Apacer, 240PIN, 1600Mb/s, 512Mx8, 0.74” Height, Micron Chips

Q3/2013	Q4/2013	Q1/2014	Q2/2014

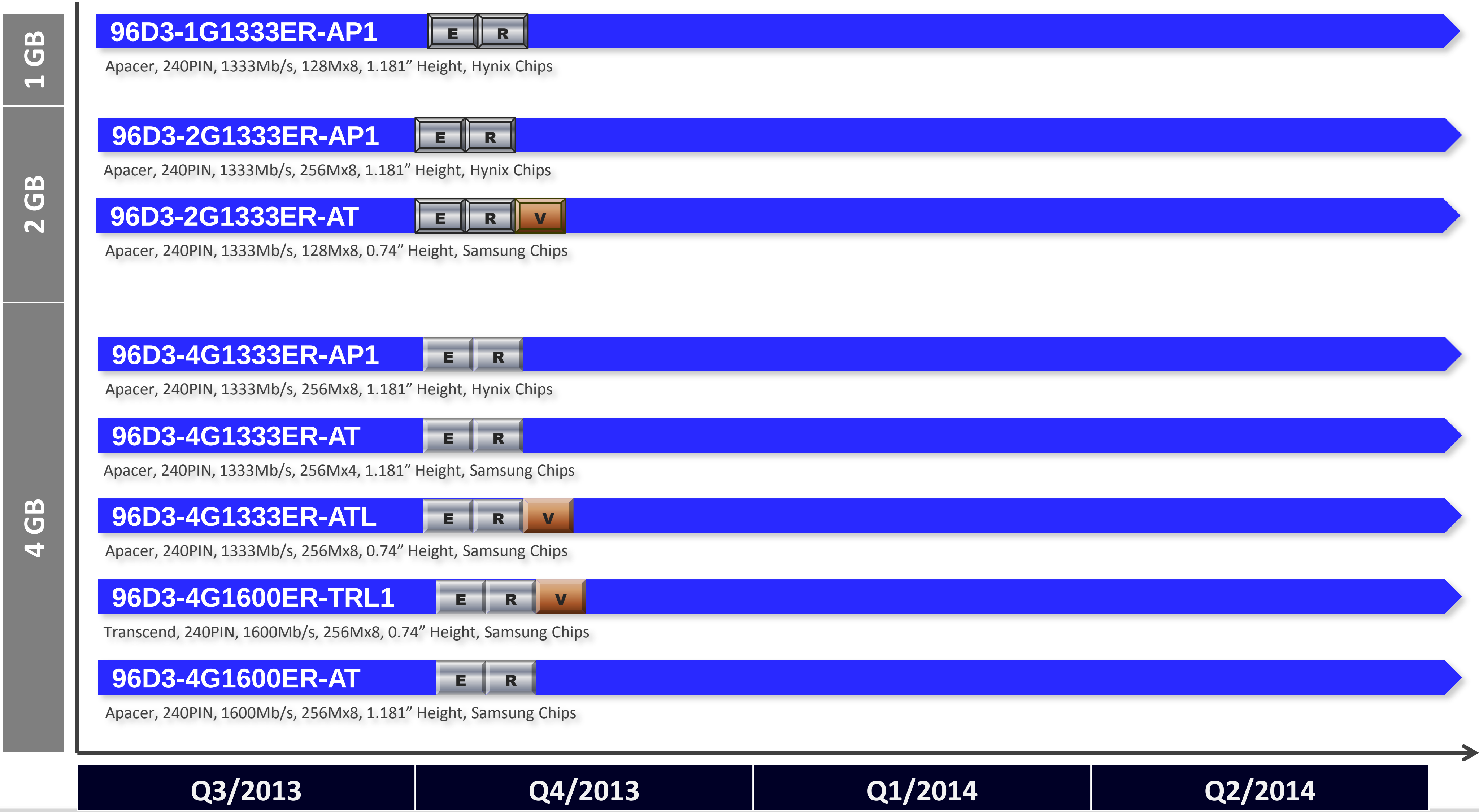
DDR3 DIMM Advance Feature

ECC and Registered

Available Phasing-out Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



1 GB

96D3-1G1333ER-AP1 E R

Apacer, 240PIN, 1333Mb/s, 128Mx8, 1.181” Height, Hynix Chips

2 GB

96D3-2G1333ER-AP1 E R

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96D3-2G1333ER-AT E R V

Apacer, 240PIN, 1333Mb/s, 128Mx8, 0.74” Height, Samsung Chips

4 GB

96D3-4G1333ER-AP1 E R

Apacer, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96D3-4G1333ER-AT E R

Apacer, 240PIN, 1333Mb/s, 256Mx4, 1.181” Height, Samsung Chips

96D3-4G1333ER-ATL E R V

Apacer, 240PIN, 1333Mb/s, 256Mx8, 0.74” Height, Samsung Chips

96D3-4G1600ER-TRL1 E R V

Transcend, 240PIN, 1600Mb/s, 256Mx8, 0.74” Height, Samsung Chips

96D3-4G1600ER-AT E R

Apacer, 240PIN, 1600Mb/s, 256Mx8, 1.181” Height, Samsung Chips

Q3/2013 Q4/2013 Q1/2014 Q2/2014

Enabling an Intelligent Planet

ADVANTECH

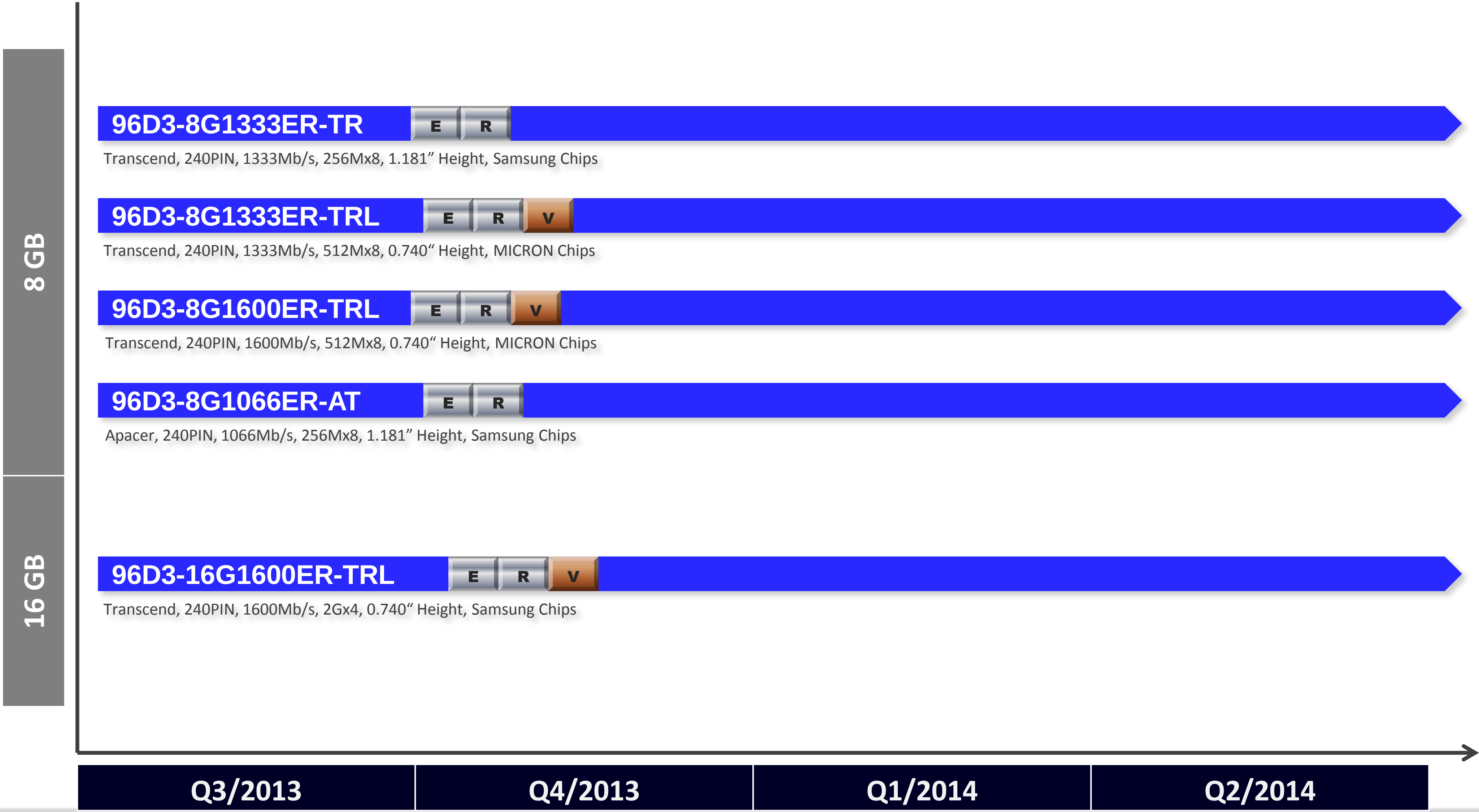
DDR3 DIMM Advance Feature

ECC and Registered

🟦 Available ▨ Phasing-out ⬜ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



96D3-8G1333ER-TR E R

Transcend, 240PIN, 1333Mb/s, 256Mx8, 1.181” Height, Samsung Chips

96D3-8G1333ER-TRL E R V

Transcend, 240PIN, 1333Mb/s, 512Mx8, 0.740“ Height, MICRON Chips

96D3-8G1600ER-TRL E R V

Transcend, 240PIN, 1600Mb/s, 512Mx8, 0.740“ Height, MICRON Chips

96D3-8G1066ER-AT E R

Apacer, 240PIN, 1066Mb/s, 256Mx8, 1.181” Height, Samsung Chips

96D3-16G1600ER-TRL E R V

Transcend, 240PIN, 1600Mb/s, 2Gx4, 0.740“ Height, Samsung Chips

DDR3 SO-DIMM

🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

1 GB

96SD3-1G1333NN-TR1

Transcend, 204PIN, 1333Mb/s, 128Mx8, 1.181” Height, Samsung Chips

96SD3-1G1333NN-AP1

Apacer, 204PIN, 1333Mb/s, 128Mx8, 1.181” Height, Hynix Chips

2 GB

96SD3-2G1333NN-TR2 Hot

Transcend, 204PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-2G1333NN-AP2

Apacer, 204PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-2G1600NN-AP

Apacer, 204PIN, 1600Mb/s, 256Mx8, 1.181” Height, Hynix Chips

Q3/2013	Q4/2013	Q1/2014	Q2/2014

DDR3 SO-DIMM

🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature

4 GB

96SD3-4G1066NN-AP

Apacer, 204PIN, 1066Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-4G1333NN-TR1

Transcend, 204PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-4G1333NN-AP1

Apacer, 204PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-4G1600NN-TR

Transcend, 204PIN, 1600Mb/s, 256Mx8, 1.181” Height, Micron Chips

96SD3-4G1600NN-AP

Apacer, 204PIN, 1600Mb/s, 256Mx8, 1.181” Height, Hynix Chips

8 GB

96SD3-8G1333NN-TR

Transcend, 204PIN, 1333Mb/s, 512Mx8, 1.181” Height, Micron Chips

96SD3-8G1600NN-TR

Transcend, 204PIN, 1600Mb/s, 512Mx8, 1.181” Height, Micron Chips

96SD3-8G1600NN-AP

Apacer, 204PIN, 1600Mb/s, 512Mx8, 1.181” Height, HYNIX Chips

96SD3-8G1600NN-AT

Apacer, 204PIN, 1600Mb/s, 512Mx8, 1.181” Height, Samsung Chips

Q3/2013	Q4/2013	Q1/2014	Q2/2014

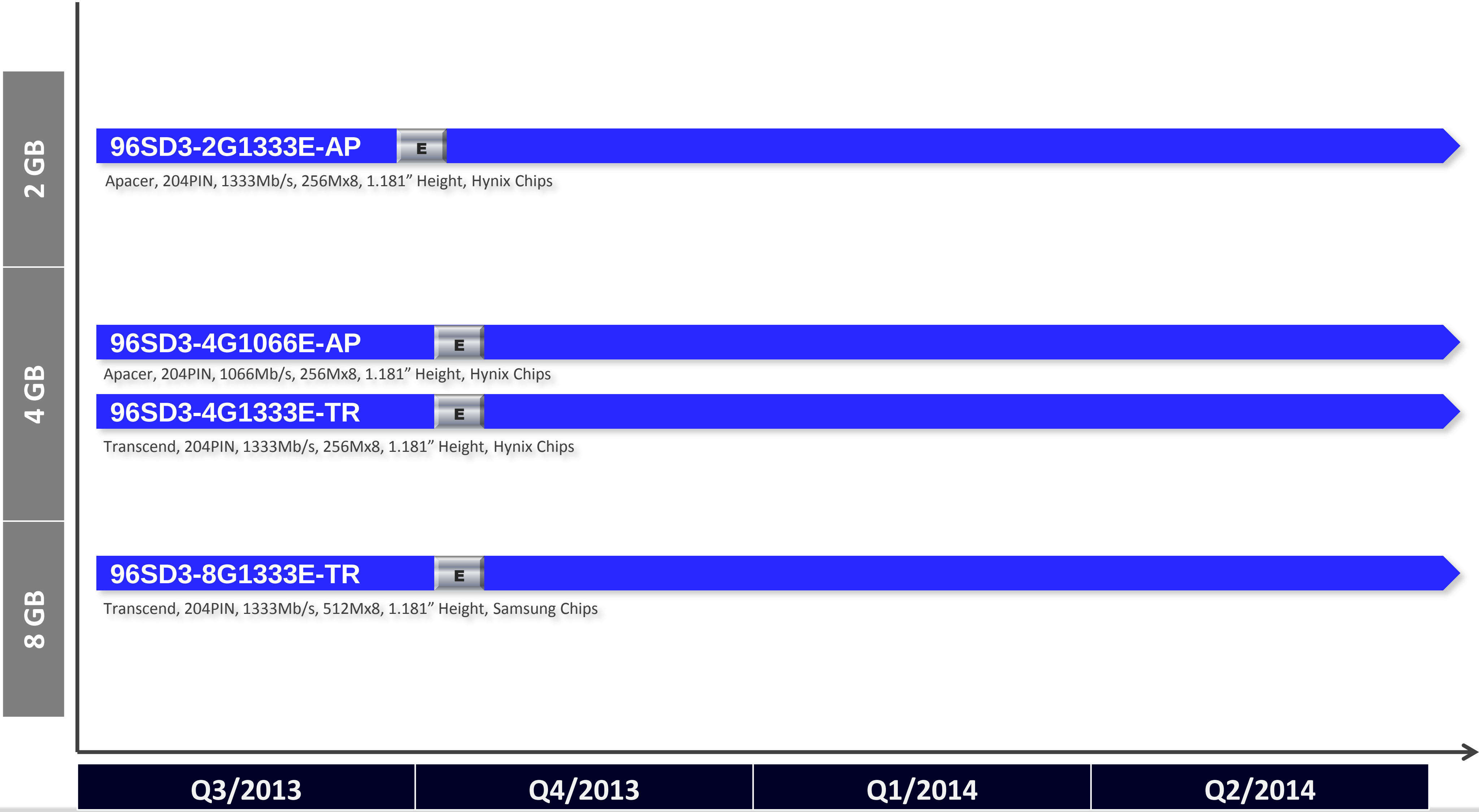
DDR3 SO-DIMM

Advance Feature - ECC

🟦 Available ▨ Phasing-out ▭ Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



96SD3-2G1333E-AP E

Apacer, 204PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-4G1066E-AP E

Apacer, 204PIN, 1066Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-4G1333E-TR E

Transcend, 204PIN, 1333Mb/s, 256Mx8, 1.181” Height, Hynix Chips

96SD3-8G1333E-TR E

Transcend, 204PIN, 1333Mb/s, 512Mx8, 1.181” Height, Samsung Chips

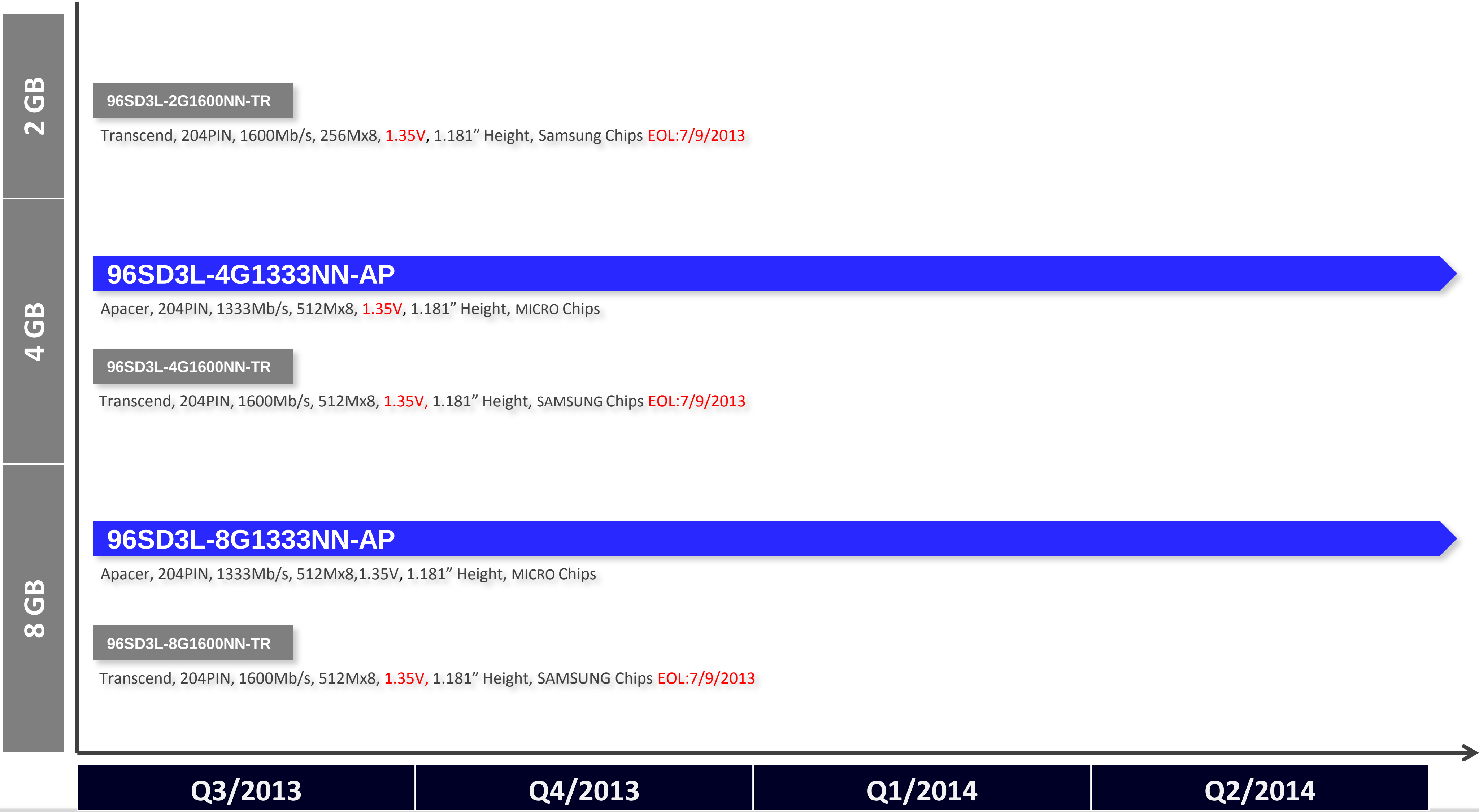
DDR3 SO-DIMM

Low Voltage.

🟦 Available ▨ Phasing-out 🟦 Planning

E ECC R Registered F Fully Buffered N New

L Low-Profile V Very Low-Profile W Wide Temperature



2 GB

96SD3L-2G1600NN-TR

Transcend, 204PIN, 1600Mb/s, 256Mx8, 1.35V, 1.181" Height, Samsung Chips EOL:7/9/2013

4 GB

96SD3L-4G1333NN-AP

Apacer, 204PIN, 1333Mb/s, 512Mx8, 1.35V, 1.181" Height, MICRO Chips

96SD3L-4G1600NN-TR

Transcend, 204PIN, 1600Mb/s, 512Mx8, 1.35V, 1.181" Height, SAMSUNG Chips EOL:7/9/2013

8 GB

96SD3L-8G1333NN-AP

Apacer, 204PIN, 1333Mb/s, 512Mx8,1.35V, 1.181" Height, MICRO Chips

96SD3L-8G1600NN-TR

Transcend, 204PIN, 1600Mb/s, 512Mx8, 1.35V, 1.181" Height, SAMSUNG Chips EOL:7/9/2013

Memory EOL Procedure

- **For support and product management optimization, PAPS will follow the Memory phase-out procedure as below.**

2 Month

1 Month

Official EOL Announcement

Last Time Buy Order

EOL

Replacement and Evaluation Approval

Thank you

MOSCHIP.RU
ВМЕСТЕ МЫ СОЗДАЕМ БУДУЩЕЕ

ПОСТАВКА
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info@moschip.ru

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Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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